PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
Stylesheet Version v1.2

EPAS ID: PAT3431176

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
FREESCALE SEMICONDUCTOR, INC.	06/06/2008

RECEIVING PARTY DATA

Name:	EVERSPIN TECHNOLOGIES, INC.
Street Address:	1347 NORTH ALMA SCHOOL ROAD
Internal Address:	SUITE 220
City:	CHANDLER
State/Country:	ARIZONA
Postal Code:	85224

PROPERTY NUMBERS Total: 152

Property Type	Number
Patent Number:	5659499
Patent Number:	5702831
Patent Number:	5734605
Patent Number:	5757695
Patent Number:	5768181
Patent Number:	5768183
Patent Number:	5818316
Patent Number:	5831920
Patent Number:	5838608
Patent Number:	5852574
Patent Number:	5861328
Patent Number:	5902690
Patent Number:	5920500
Patent Number:	5930164
Patent Number:	5940319
Patent Number:	5946227
Patent Number:	5953248
Patent Number:	5959880
Patent Number:	5966323

Property Type	Number
Patent Number:	5978257
Patent Number:	6024885
Patent Number:	6055178
Patent Number:	6083764
Patent Number:	6111781
Patent Number:	6165803
Patent Number:	6169689
Patent Number:	6174737
Patent Number:	6177204
Patent Number:	6191973
Patent Number:	6205052
Patent Number:	6205073
Patent Number:	6211090
Patent Number:	6211559
Patent Number:	6233172
Patent Number:	6252795
Patent Number:	6261646
Patent Number:	6272040
Patent Number:	6272041
Patent Number:	6278631
Patent Number:	6285581
Patent Number:	6292389
Patent Number:	6304477
Patent Number:	6314020
Patent Number:	6376260
Patent Number:	6392923
Patent Number:	6395595
Patent Number:	6418046
Patent Number:	6445612
Patent Number:	6452823
Patent Number:	6469926
Patent Number:	6515895
Patent Number:	6544801
Patent Number:	6545906
Patent Number:	6549454
Patent Number:	6609174
Patent Number:	6657889
Patent Number:	6693824

Property Type	Number
Patent Number:	6711052
Patent Number:	6711068
Patent Number:	6714440
Patent Number:	6714442
Patent Number:	6714446
Patent Number:	6720597
Patent Number:	6744663
Patent Number:	6750068
Patent Number:	6760266
Patent Number:	6783637
Patent Number:	6783994
Patent Number:	6784510
Patent Number:	6798004
Patent Number:	6801415
Patent Number:	6818961
Patent Number:	6829158
Patent Number:	6831312
Patent Number:	6835423
Patent Number:	6842365
Patent Number:	6881351
Patent Number:	6885074
Patent Number:	6888743
Patent Number:	6890770
Patent Number:	6898112
Patent Number:	6903964
Patent Number:	6909631
Patent Number:	6911156
Patent Number:	6916669
Patent Number:	6936763
Patent Number:	6943038
Patent Number:	6944052
Patent Number:	6946697
Patent Number:	6956764
Patent Number:	6967366
Patent Number:	7031183
Patent Number:	7042025
Patent Number:	7067331
Patent Number:	7087972

Property Type	Number
Patent Number:	7095646
Patent Number:	7098495
Patent Number:	7105903
Patent Number:	7129098
Patent Number:	7144744
Patent Number:	7149106
Patent Number:	7154772
Patent Number:	7169622
Patent Number:	7170706
Patent Number:	7172904
Patent Number:	7184300
Patent Number:	7220602
Patent Number:	7224630
Patent Number:	7245527
Patent Number:	7264985
Patent Number:	7271011
Patent Number:	7285835
Patent Number:	7292484
Patent Number:	7324369
Patent Number:	7329935
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Patent Number:	7370260
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Patent Number:	7414396
Patent Number:	7432150
Patent Number:	7444738
Patent Number:	7445943
Patent Number:	7465589
Patent Number:	7476329
Patent Number:	7502253
Patent Number:	7510883
Patent Number:	7511990
Patent Number:	7532533
Patent Number:	7541804
Patent Number:	7543211
Patent Number:	7572645
Patent Number:	7602177
Patent Number:	7605437

Property Type	Number
Patent Number:	7635654
Patent Number:	7635902
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Patent Number:	7683445
Patent Number:	7684161
Patent Number:	7697321
Patent Number:	7747926
Patent Number:	7829980
Patent Number:	7888756
Patent Number:	7932571
Patent Number:	7965077
Patent Number:	8119424
Patent Number:	8216703
Patent Number:	8237437
Patent Number:	8242776
Patent Number:	8497538
Patent Number:	8508004
Patent Number:	8754460
Application Number:	14303200

CORRESPONDENCE DATA

Fax Number: (202)450-5538

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

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Address Line 2: SUITE 450

Address Line 4: WASHINGTON, D.C. 20037

NAME OF SUBMITTER:	KIRSTEN JOHNSON
SIGNATURE:	/Kirsten Johnson/
DATE SIGNED:	07/09/2015

Total Attachments: 32

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Intellectual Property Assignment for Assigned Patents

Pursuant to the terms and conditions of a certain Intellectual Property Agreement dated as of June 6, 2008 (the "IPA") between Freescale Semiconductor, Inc., a corporation organized and existing under the laws of the State of Delaware ("**Assignor**") hereby assigns, transfers and sets over to Everspin Technologies, Inc., a corporation organized and existing under the laws of Delaware ("**Assignee**"), Assignor assigns its entire right, title and interest for the United States of America and its territorial possessions, and all foreign countries including all rights of priority, in and to the patents and patent applications set forth on Schedule A hereto and all reissues and reexaminations thereof, and all divisionals, continuations, and continuations-in-part (to the extent they claim inventions claimed and disclosed in the patents listed above) thereof existing as of the date hereof, and all inventions disclosed therein, together with all claims for damages by reason of past or future infringement, with the right to sue for and collect the same for the use and benefit of Assignor and its successors and assigns.

Assignor agrees to execute all applications, amended specifications, deeds or other instruments, and to do all acts necessary or proper to vest and confirm in Assignee, its successors and assigns, the legal title to all such patents and patent applications.

Assignor does hereby authorize and request the Commissioner of Patents and Trademarks of the United States to issue such Letters Patent as shall be granted upon said inventions or applications based thereon to Assignee, its successors and assigns.

This assignment of patents and applications is delivered subject to and pursuant to the terms and conditions of the IPA and the rights and obligations of Assignor and Assignee set forth in the representations, warranties, covenants, indemnities and other terms and provisions of the IPA shall not be limited, altered, impaired, enhanced or enlarged hereby or by the performance hereunder.

Witness my hand and seal this 6th day of June, 2008.

Name:
Title:

County of TRAVIS)
State of TEXAS)

On this 6 day of June, 2008, before me, the undersigned notary public, personally appeared Lisa Su, proved to me through satisfactory evidence of identification, which was DL, to be the person whose name is signed on the preceding document, and acknowledged to me that he signed it voluntarily for its stated purpose.

[affix seal]

JENNIFER S. GENTRY NOTARY PUBLIC STATE OF TEXAS 1-31-2010

Notary Public

My commission expires: 1/31/2010

Schedule A

List of Assigned Patents

Assigned Patents

Status	Docket #	Cty	App #	App Dt	Natl File Dt	Patent #	Grant Dt	Title
FILED	CML00234CR	CHIN	200480010863.1	07-May-04	21-Oct-05			MAGNETOELECTRONICS INFORMATION DEVICE HAVING A COMPOUND MAGNETIC FREE LAYER
GRANTED	CML00234CR	FRAN	04775950.1	07-May-04	13-Dec-05	EP1625589	23-Apr-08	MAGNETOELECTRONICS INFORMATION DEVICE HAVING A COMPOUND MAGNETIC FREE LAYER
GRANTED	CML00234CR	GBRI	04775950.1	07-May-04	13-Dec-05	EP1625589	23-Apr-08	MAGNETOELECTRONICS INFORMATION DEVICE HAVING A COMPOUND MAGNETIC FREE LAYER
GRANTED	CML00234CR	GERM	04775950.1	07-May-04	13-Dec-05	602004013305.1	23-Apr-08	MAGNETOELECTRONICS INFORMATION DEVICE HAVING A COMPOUND MAGNETIC FREE LAYER
FILED	CML00234CR	INDI	4158/DELNP/2005	07-May-04	15-Sep-05			MAGNETOELECTRONICS INFORMATION DEVICE HAVING A COMPOUND MAGNETIC FREE LAYER
FILED	CML00234CR	JAPA	2006-532843	07-May-04	14-Nov-05			MAGNETOELECTRONICS INFORMATION DEVICE HAVING A COMPOUND MAGNETIC FREE LAYER
FILED	CML00234CR	KORS	10-2005-7021545	07-May-04	11-Nov-05			MAGNETOELECTRONICS INFORMATION DEVICE HAVING A COMPOUND MAGNETIC FREE LAYER
GRANTED	CML00234CR	USA	10/437831	13-May-03		6714446	30-Mar-04	MAGNETOELECTRONICS INFORMATION DEVICE HAVING A COMPOUND MAGNETIC FREE LAYER
GRANTED	CML00237CR	USA	10/209524	31-Jul-02		7172904	06-Feb-07	HIGH SENSITIVITY SENSOR FOR TAGGED MAGNETIC BEAD BIOASSAYS
FILED	CML00237CR	USA	11/616142	26-Dec-06				HIGH SENSITIVITY SENSOR FOR TAGGED MAGNETIC BEAD BIOASSAYS
GRANTED	CML00245CR	CHIN	03820540.8	24-Jul-03	28-Feb-05	ZL03820540.8	26-Sep-07	NANOCRYSTALLINE LAYERS FOR IMPROVED MRAM TUNNEL JUNCTIONS
FILED	CML00245CR	JAPA	2005-500435	24-Jul-03	25-Feb-05			NANOCRYSTALLINE LAYERS FOR IMPROVED MRAM TUNNEL JUNCTIONS
FILED	CML00245CR	KORS	PCT/US03/23063	24-Jul-03	04-May-05			NANOCRYSTALLINE LAYERS FOR IMPROVED MRAM TUNNEL JUNCTIONS
FILED	CML00245CR	TAIW	092121639	07-Aug-03				NANOCRYSTALLINE LAYERS FOR IMPROVED MRAM TUNNEL JUNCTIONS
GRANTED	CML00245CR	USA	10/232111	30-Aug-02		6801415	05-Oct-04	NANOCRYSTALLINE LAYERS FOR IMPROVED MRAM TUNNEL JUNCTIONS
GRANTED	CML00246CR	CHIN	03820541.6	25-Jul-03	28-Feb-05	ZL03820541.6	26-Sep-07	AMORPHOUS ALLOYS FOR MAGNETIC DEVICES

FILED	CML00246CR	JAPA	2004-532831	25-Jul-03	25-Feb-05			AMORPHOUS ALLOYS FOR MAGNETIC DEVICES
GRANTED	CML00246CR	USA	10/232164	30-Aug-02		6831312	14-Dec-04	AMORPHOUS ALLOYS FOR MAGNETIC DEVICES
GRANTED	CML00246CR	USA	10/980930	03-Nov-04		7067331	27-Jun-06	AMORPHOUS ALLOYS FOR MAGNETIC DEVICES
FILED	CML00284CR	CHIN	200380106461.7	28-Oct-03				SYNTHETIC ANTIFERROMAGNETIC STRUCTURE FOR MAGNETOELECTRONIC DEVICES
FILED	CML00284CR	JAPA	2004-564826	28-Oct-03	20-Jun-05			SYNTHETIC ANTIFERROMAGNETIC STRUCTURE FOR MAGNETOELECTRONIC DEVICES
FILED	CML00284CR	KORS	10-2005-7011209	28-Oct-03	17-Jun-05			SYNTHETIC ANTIFERROMAGNETIC STRUCTURE FOR MAGNETOELECTRONIC DEVICES
FILED	CML00284CR	TAIW	092131682	12-Nov-03				SYNTHETIC ANTIFERROMAGNETIC STRUCTURE FOR MAGNETOELECTRONIC DEVICES
GRANTED	CML00284CR	USA	10/322979	18-Dec-02		6898112	24-May-05	SYNTHETIC ANTIFERROMAGNETIC STRUCTURE FOR MAGNETOELECTRONIC DEVICES
GRANTED	CML00284CR	USA	11/075587	09-Mar-05		7235408	26-Jun-07	SYNTHETIC ANTIFERROMAGNETIC STRUCTURE FOR MAGNETOELECTRONIC DEVICES
GRANTED	CML00285CR	USA	10/285161	31-Oct-02		6783637	31-Aug-04	HIGH THROUGHPUT DUAL ION BEAM DEPOSITION APPARATUS
FILED	CML00320CR	CHIN	200480024513.0	03-Aug-04	27-Feb-06			METHOD OF WRITING TO A MULTI-STATE MAGNETIC RANDOM ACCESS MEMORY CELL
FILED	CML00320CR	KORS	10-2006-7003624	03-Aug-04	22-Feb-06			METHOD OF WRITING TO A MULTI-STATE MAGNETIC RANDOM ACCESS MEMORY CELL
GRANTED	CML00320CR	USA	10/647976	25-Aug-03		6956764	18-Oct-05	METHOD OF WRITING TO A MULTI-STATE MAGNETIC RANDOM ACCESS MEMORY CELL
FILED	CML00331CR	EPC	04776982.3	22-Jun-04	23-Dec-05			OBLIQUE DEPOSITION TO INDUCE MAGNETIC ANISOTROPY FOR MRAM CELLS
FILED	CML00331CR	JAPA	2006-517586	22-Jun-04	20-Dec-05			OBLIQUE DEPOSITION TO INDUCE MAGNETIC ANISOTROPY FOR MRAM CELLS
FILED	CML00331CR	KORS	10-2005-7025176	22-Jun-04	28-Dec-05			OBLIQUE DEPOSITION TO INDUCE MAGNETIC ANISOTROPY FOR MRAM CELLS
FILED	CML00331CR	PCT	PCT/US04/20156	22-Jun-04				OBLIQUE DEPOSITION TO INDUCE MAGNETIC ANISOTROPY FOR MRAM CELLS
GRANTED	CML00331CR	USA	10/611789	30-Jun-03		6818961	16-Nov-04	OBLIQUE DEPOSITION TO INDUCE MAGNETIC ANISOTROPY FOR MRAM CELLS
FILED	CML00378CR	KORS	10-2006-7003756	06-Aug-04	24-Feb-06			MAGNETORESISTIVE RANDOM ACCESS MEMORY WITH REDUCED SWITCHING FIELD VARIATION

FILED	CML00378CR	PCT	PCT/US04/25832	06-Aug-04				MAGNETORESISTIVE RANDOM ACCESS MEMORY WITH REDUCED SWITCHING FIELD VARIATION
GRANTED	CML00378CR	SING	200600334-7	06-Aug-04		118976	30-Apr-07	MAGNETORESISTIVE RANDOM ACCESS MEMORY WITH REDUCED SWITCHING FIELD VARIATION
FILED	CML00378CR	TAIW	093125242	20-Aug-04				MAGNETORESISTIVE RANDOM ACCESS MEMORY WITH REDUCED SWITCHING FIELD VARIATION
GRANTED	CML00378CR	USA	10/648466	25-Aug-03		6967366	22-Nov-05	MAGNETORESISTIVE RANDOM ACCESS MEMORY WITH REDUCED SWITCHING FIELD VARIATION
FILED	CML00378CR	USA	11/240179	29-Sep-05				MAGNETORESISTIVE RANDOM ACCESS MEMORY WITH REDUCED SWITCHING FIELD VARIATION
FILED	CML00379CR	CHIN	03817782.X	11-Jul-03	25-Jan-05			MAGNETORESISTANCE RANDOM ACCESS MEMORY
FILED	CML00379CR	JAPA	2004-524584	11-Jul-03	25-Jan-05			MAGNETORESISTANCE RANDOM ACCESS MEMORY
FILED	CML00379CR	KORS	10-2005-7001777	11-Jul-03	31-Jan-05			MAGNETORESISTANCE RANDOM ACCESS MEMORY
FILED	CML00379CR	TAIW	092120223	24-Jul-03				MAGNETORESISTANCE RANDOM ACCESS MEMORY
GRANTED	CML00379CR	USA	10/209156	31-Jul-02		6654278	25-Nov-03	MAGNETORESISTANCE RANDOM ACCESS MEMORY
GRANTED	CR00-002	CHIN	01814932.4	09-Aug-01	28-Feb-03	ZL01814932.4	25-Oct-06	HIGH DENSITY MRAM CELL ARRAY
FILED	CR00-002	JAPA	2002-524191	09-Aug-01				HIGH DENSITY MRAM CELL ARRAY
GRANTED	CR00-002	KORS	10-2003-7003128	09-Aug-01		785261	06-Dec-07	HIGH DENSITY MRAM CELL ARRAY
GRANTED	CR00-002	SING	200300779-6	09-Aug-01	24-Feb-03	95073	31-May-05	HIGH DENSITY MRAM CELL ARRAY
GRANTED	CR00-002	TAIW	90121070	11-Sep-01		NI-175733	07-Aug-03	COMPACT MRAM CELL, COMPACT MAGNETIC TUNNEL JUNCTION MEMORY CELL, AND FABRICATING METHOD THEREOF
GRANTED	CR00-002	USA	09/649114	28-Aug-00		6365419	02-Apr-02	HIGH DENSITY MRAM CELL ARRAY
GRANTED	CR00-004	TAIW	91102003	05-Feb-02		NI-191785	25-Mar-04	MAGNETOELECTRONICS ELEMENT HAVING A STRESSED OVER-LAYER CONFIGURED FOR ALTERATION OF THE SWITCHING ENERGY BARRIER
GRANTED	CR00-004	USA	09/792466	26-Feb-01		6515341	04-Feb-03	MAGNETOELECTRONICS ELEMENT HAVING A STRESSED OVER-LAYER CONFIGURED FOR ALTERATION OF THE SWITCHING ENERGY BARRIER
FILED	CR00-005	CHIN	02804400.2	11-Jan-02	31-Jul-03			CONTENT ADDRESSABLE MAGNETIC RANDOM ACCESS MEMORY
GRANTED	CR00-005	JAPA	2002-561835	11-Jan-02	31-Jul-03	3793507	14-Apr-06	CONTENT ADDRESSABLE MAGNETIC

								RANDOM ACCESS MEMORY
FILED	CR00-005	KORS	10-2003-7010125	11-Jan-02				CONTENT ADDRESSABLE MAGNETIC RANDOM ACCESS MEMORY
GRANTED	CR00-005	TAIW	91101370	28-Jan-02		NI-191782	25-Mar-04	CONTENT ADDRESSABLE MAGNETIC RANDOM ACCESS MEMORY
GRANTED	CR00-005	USA	09/774934	31-Jan-01		6304477	16-Oct-01	CONTENT ADDRESSABLE MAGNETIC RANDOM ACCESS MEMORY
GRANTED	CR00-006	TAIW	91101374	28-Jan-02		NI-172793	25-Jun-03	NON-VOLATILE MAGNETIC REGISTER
GRANTED	CR00-006	USA	09/774949	31-Jan-01		6515895	04-Feb-03	NON-VOLATILE MAGNETIC REGISTER
GRANTED	CR00-007	USA	09/695467	24-Oct-00		6579625	17-Jun-03	MAGNETOELECTRONICS ELEMENT HAVING A MAGNETIC LAYER FORMED OF MULTIPLE SUB-ELEMENT LAYERS
FILED	CR00-010	CHIN	01815003.9	24-Aug-01	28-Feb-03			MTJ MRAM SERIES-PARALLEL ARCHITECTURE
FILED	CR00-010	HONG	04109873.9	14-Dec-04				MTJ MRAM SERIES-PARALLEL ARCHITECTURE
FILED	CR00-010	JAPA	2002-524150	24-Aug-01	28-Feb-03			MTJ MRAM SERIES-PARALLEL ARCHITECTURE
FILED	CR00-010	KORS	10-2003-7003095	24-Aug-01				MTJ MRAM SERIES-PARALLEL ARCHITECTURE
GRANTED	CR00-010	TAIW	90121078	27-Aug-01		NI-171883	10-Jun-03	MTJ MRAM SERIES-PARALLEL ARCHITECTURE
GRANTED	CR00-010	USA	09/649117	28-Aug-00		6331943	18-Dec-01	MTJ MRAM SERIES-PARALLEL ARCHITECTURE
FILED	CR00-013	CHIN	01815778.5	17-Aug-01				MTJ MRAM PARALLEL-PARALLEL ARCHITECTURE
FILED	CR00-013	JAPA	2002-524149	17-Aug-01				MTJ MRAM PARALLEL-PARALLEL ARCHITECTURE
GRANTED	CR00-013	TAIW	90121069	27-Aug-01		NI-200025	04-Aug-04	MTJ MRAM PARALLEL-PARALLEL ARCHITECTURE
GRANTED	CR00-013	USA	09/649562	28-Aug-00		6272041	07-Aug-01	MTJ MRAM PARALLEL-PARALLEL ARCHITECTURE
FILED	CR00-014	CHIN	02804398.7	11-Jan-02				NON-VOLATILE MAGNETIC CACHE MEMORY
FILED	CR00-014	JAPA	2002-561836	11-Jan-02				NON-VOLATILE MAGNETIC CACHE MEMORY
FILED	CR00-014	KORS	10-2003-7010157	11-Jan-02				NON-VOLATILE MAGNETIC CACHE MEMORY
GRANTED	CR00-014	TAIW	91101366	28-Jan-02		NI-183360	04-Dec-03	NON-VOLATILE MAGNETIC CACHE MEMORY AND METHOD OF USE
GRANTED	CR00-014	USA	09/774983	31-Jan-01		6452823	17-Sep-02	NON-VOLATILE MAGNETIC CACHE MEMORY AND METHOD OF USE
FILED	CR00-016	CHIN	01816749.7	28-Sep-01	02-Apr-03			TUNELLING MAGNETORESISTANCE (TMR) MATERIAL HAVING ULTRA-THIN MAGNETIC LAYER
GRANTED	CR00-016	USA	09/677505	02-Oct-00		6549454	15-Apr-03	TMR MATERIAL HAVING A SUBSTANTIALLY SMOOTH AND CONTINUOUS ULTRA-THIN

								MAGNETIC LAYER
GRANTED	CR00-021	TAIW	091118407	15-Aug-02		NI-200673	16-Aug-04	MAGNETO-ELECTRONIC COMPONENT
GRANTED	CR00-021	USA	09/940263	27-Aug-01		6430084	06-Aug-02	MAGNETO-ELECTRONIC COMPONENT
FILED	CR00-027	CHIN	02825450.3	13-Dec-02				MAGNETO-ELECTRONIC COMPONENT
GRANTED	CR00-027	USA	10/029085	21-Dec-01		6525957	25-Feb-03	MAGNETO-ELECTRONIC COMPONENT AND METHOD OF MANUFACTURING
GRANTED	CR00-038	TAIW	091118405	15-Aug-02		NI-204637	14-Oct-04	MAGNETO-ELECTRONIC COMPONENT
GRANTED	CR00-038	USA	09/940319	27-Aug-01		6430085	06-Aug-02	MAGNETO-ELECTRONIC COMPONENT AND METHOD OF MANUFACTURE
FILED	CR00-039	CHIN	03805492.2	27-Feb-03	01-Oct-04			CLADDING MATERIAL ON CONDUCTIVE LINES OF MRAM
FILED	CR00-039	EPC	03709387.9	27-Feb-03	22-Sep-04			CLADDING MATERIAL ON CONDUCTIVE LINES OF MRAM
FILED	CR00-039	JAPA	2003-575387	27-Feb-03				CLADDING MATERIAL ON CONDUCTIVE LINES OF MRAM
GRANTED	CR00-039	KORS	10-2004-7014056	27-Feb-03	08-Sep-04	698803	16-Mar-07	CLADDING MATERIAL ON CONDUCTIVE LINES OF MRAM
GRANTED	CR00-039	TAIW	092104917	07-Mar-03		I283885	11-Jul-07	METHOD OF APPLYING CLADDING MATERIAL ON CONDUCTIVE LINES OF MRAM DEVICES
GRANTED	CR00-039	USA	10/093909	08-Mar-02		6927072	09-Aug-05	METHOD OF APPLYING CLADDING MATERIAL ON CONDUCTIVE LINES OF MRAM DEVICES
FILED	CR00-039	USA	11/139143	26-May-05				METHOD OF APPLYING CLADDING MATERIAL ON CONDUCTIVE LINES OF MRAM DEVICES
FILED	CR00-040	CHIN	01821783.4	26-Dec-01				MRAM WRITE APPARATUS AND METHOD
FILED	CR00-040	JAPA	2002-555419	26-Dec-01				MRAM WRITE APPARATUS AND METHOD
GRANTED	CR00-040	TAIW	91100004	02-Jan-02		NI-183353	04-Dec-03	MRAM WRITE APPARATUS AND METHOD
GRANTED	CR00-040	USA	09/754458	04-Jan-01		6351409	26-Feb-02	MRAM WRITE APPARATUS AND METHOD
FILED	CR00-043	CHIN	02822705.0	24-Sep-02				WRITING TO A SCALABLE MRAM ELEMENT
FILED	CR00-043	HONG	05107472.7	25-Aug-05				WRITING TO A SCALABLE MRAM ELEMENT
FILED	CR00-043	JAPA	2003-537077	24-Sep-02	16-Apr-04			WRITING TO A SCALABLE MRAM ELEMENT
FILED	CR00-043	KORS	10-2004-7006280	24-Sep-02	16-Apr-04			WRITING TO A SCALABLE MRAM ELEMENT
GRANTED	CR00-043	SING	200402835-3	24-Sep-02		113621	31-Aug-06	WRITING TO A SCALABLE MRAM ELEMENT
GRANTED	CR00-043	TAIW	091123192	08-Oct-02		NI-199559	27-Jul-04	WRITING TO A SCALABLE MRAM ELEMENT
GRANTED	CR00-043	USA	09/978859	16-Oct-01		6545906	08-Apr-03	A METHOD OF WRITING TO A SCALABLE MAGNETORESISTANCE RANDOM ACCESS TO MEMORY ELEMENT
GRANTED	CR00-043	USA	10/339378	09-Jan-03		7184300	27-Feb-07	METHOD OF WRITING TO A SCALABLE MAGNETORESISTANCE RANDOM ACCESS TO MEMORY ELEMENT
GRANTED	CR00-051	USA	10/109429	28-Mar-02		6518071	11-Feb-03	A MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE AND METHOD OF FABRICATION THEREOF

GRANTED	CR00-052	TAIW	91101368	28-Jan-02		NI-183622	09-Dec-03	REFERENCE VOLTAGE GENERATOR FOR MRAM AND METHOD
GRANTED	CR00-052	USA	09/772668	30-Jan-01		6385109	07-May-02	REFERENCE VOLTAGE GENERATOR FOR MRAM AND METHOD
GRANTED	CR00-052	USA	10/090905	05-Mar-02		6496436	17-Dec-02	REFERENCE VOLTAGE GENERATOR FOR MRAM AND METHOD
FILED	CR00-053	CHIN	02804340.5	11-Jan-02				MRAM ARCHITECTURE AND SYSTEM
FILED	CR00-053	EPC	02709023.2	11-Jan-02				MRAM ARCHITECTURE AND SYSTEM
FILED	CR00-053	HONG	04106740.6	07-Sep-04				MRAM ARCHITECTURE AND SYSTEM
FILED	CR00-053	JAPA	2002-561833	11-Jan-02				MRAM ARCHITECTURE AND SYSTEM
FILED	CR00-053	KORS	10-2003-7010082	11-Jan-02				MRAM ARCHITECTURE AND SYSTEM
GRANTED	CR00-053	TAIW	91101369	28-Jan-02		NI-183623	09-Dec-03	MRAM ARCHITECTURE AND SYSTEM
GRANTED	CR00-053	USA	09/772669	30-Jan-01		6418046	09-Jul-02	MRAM ARCHITECTURE AND SYSTEM
GRANTED	CR00-053	USA	10/141161	08-May-02		6552927	22-Apr-03	MRAM ARCHITECTURE AND SYSTEM
GRANTED	CR01-004	USA	10/095816	12-Mar-02		6812040	02-Nov-04	A METHOD OF FABRICATING A SELF-ALIGNED VIA CONTACT FOR A MAGNETIC MEMORY ELEMENT
GRANTED	CR01-005	USA	10/133136	26-Apr-02		6783994	31-Aug-04	A METHOD OF FABRICATING A SELF-ALIGNED MAGNETIC TUNNELING JUNCTION AND VIA CONTACT
GRANTED	CR01-006	TAIW	91103030	21-Feb-02		NI-199608	28-Jul-04	MAGNETORESISTIVE MIDPOINT GENERATOR AND METHOD
GRANTED	CR01-006	USA	09/793163	27-Feb-01		6392923	21-May-02	MAGNETORESISTIVE MIDPOINT GENERATOR AND METHOD
FILED	CR01-013	JAPA	2004-523033	27-Jun-03	30-Nov-04			MULTI-STATE MRAM WITH IMPROVED STORAGE DENSITY
FILED	CR01-013	KORS	10-2005-7000876	27-Jun-03	17-Jan-05			MULTI-STATE MRAM WITH IMPROVED STORAGE DENSITY
GRANTED	CR01-013	USA	10/198203	17-Jul-02		7095646	22-Aug-06	MULTI-STATE MAGNETORESISTANCE RANDOM ACCESS CELL WITH IMPROVED MEMORY STORAGE DENSITY
FILED	CR01-013	USA	11/212321	25-Aug-05				MULTI-STATE MAGNETORESISTANCE RANDOM ACCESS CELL WITH IMPROVED MEMORY STORAGE DENSITY
FILED	CR01-020	CHIN	02816360.5	02-Aug-02	20-Feb-04			MAGNETORESISTIVE LEVEL GENERATOR
FILED	CR01-020	JAPA	2002-522935	02-Aug-02	20-Feb-04			MAGNETORESISTIVE LEVEL GENERATOR
FILED	CR01-020	KORS	10-2004-7002504	02-Aug-02	20-Feb-04			MAGNETORESISTIVE LEVEL GENERATOR
GRANTED	CR01-020	TAIW	091118402	15-Aug-02		I235369	01-Jul-05	MAGNETORESISTIVE LEVEL GENERATOR AND METHOD
GRANTED	CR01-020	USA	09/935269	22-Aug-01		6829158	07-Dec-04	MAGNETORESISTIVE LEVEL GENERATOR AND METHOD
FILED	CR01-021	CHIN	03802403.9	09-Jan-03				MRAM WITHOUT ISOLATION DEVICES

GRANTED	CR01-021	FRAN	03731902.7	09-Jan-03	10-Aug-04	EP1476875	16-Jan-08	MRAM WITHOUT ISOLATION DEVICES
GRANTED	CR01-021	GBRI	03731902.7	09-Jan-03	10-Aug-04	EP1476875	16-Jan-08	MRAM WITHOUT ISOLATION DEVICES
GRANTED	CR01-021	GERM	03731902.7	09-Jan-03	10-Aug-04	60318631.1	16-Jan-08	MRAM WITHOUT ISOLATION DEVICES
FILED	CR01-021	JAPA	2003-562942	09-Jan-03	20-Jul-04			MRAM WITHOUT ISOLATION DEVICES
FILED	CR01-021	KORS	10-2004-7011128	09-Jan-03	19-Jul-04			MRAM WITHOUT ISOLATION DEVICES
GRANTED	CR01-021	TAIW	092101010	17-Jan-03		I283404	01-Jul-07	MRAM WITHOUT ISOLATION DEVICES
GRANTED	CR01-021	USA	10/051646	18-Jan-02		6512689	28-Jan-03	MRAM WITHOUT ISOLATION DEVICES
GRANTED	CR01-022	USA	10/010363	13-Nov-01		6720597	13-Apr-04	CLADDING OF A CONDUCTIVE INTERCONNECT FOR PROGRAMMING A MRAM DEVICE USING MULTIPLE MAGNETIC LAYERS
FILED	CR01-023	CHIN	02822806.5	24-Sep-02	17-May-04			MAGNETORESISTANCE RANDOM ACCESS MEMORY FOR IMPROVED SCALABILITY
FILED	CR01-023	JAPA	2003-544760	24-Sep-02	16-Apr-04			MAGNETORESISTANCE RANDOM ACCESS MEMORY FOR IMPROVED SCALABILITY
FILED	CR01-023	KORS	10-2004-7006283	24-Sep-02	16-Apr-04			MAGNETORESISTANCE RANDOM ACCESS MEMORY FOR IMPROVED SCALABILITY
GRANTED	CR01-023	SING	200402752-0	24-Sep-02		105632	31-May-06	MAGNETORESISTANCE RANDOM ACCESS MEMORY FOR IMPROVED SCALABILITY
GRANTED	CR01-023	TAIW	091123191	08-Oct-02		NI-195271	14-May-04	MAGNETORESISTANCE RANDOM ACCESS MEMORY FOR IMPROVED SCALABILITY
GRANTED	CR01-023	USA	09/978860	16-Oct-01		6531723	11-Mar-03	MAGNETORESISTANCE RANDOM ACCESS MEMORY FOR IMPROVED SCALABILITY
FILED	CR01-023	USA	11/077398	10-Mar-05				MAGNETORESISTANCE RANDOM ACCESS MEMORY FOR IMPROVED SCALABILITY
GRANTED	CR01-033	USA	10/010812	13-Nov-01		6501144	31-Dec-02	A CONDUCTIVE LINE WITH MULTIPLE TURNS FOR PROGRAMMING A MRAM DEVICE
FILED	CR01-034	JAPA	2003-544761	30-Oct-02				CLADDING FIELD ENHANCEMENT OF A MRAM DEVICE
FILED	CR01-034	TAIW	091132400	01-Nov-02				NARROW GAP CLADDING FIELD ENHANCEMENT FOR LOW POWER PROGRAMMING OF A MRAM DEVICE
GRANTED	CR01-034	USA	10/010574	13-Nov-01		6559511	06-May-03	NARROW GAP CLADDING FIELD ENHANCEMENT FOR LOW POWER PROGRAMMING OF A MRAM DEVICE
FILED	CR01-035	CHIN	03815278.9	18-Jun-03	28-Dec-04			MAGNETIC SHIELDING FOR ELECTRONIC CIRCUITS WHICH INCLUDE MAGNETIC MATERIALS
GRANTED	CR01-035	FRAN	03742062.7	18-Jun-03	15-Dec-04	EP1518451	16-Apr-08	MAGNETIC SHIELDING FOR ELECTRONIC CIRCUITS WHICH INCLUDE MAGNETIC MATERIALS
GRANTED	CR01-035	GBRI	03742062.7	18-Jun-03	15-Dec-04	EP1518451	16-Apr-08	MAGNETIC SHIELDING FOR ELECTRONIC CIRCUITS WHICH INCLUDE MAGNETIC MATERIALS

GRANTED	CR01-035	GERM	03742062.7	18-Jun-03	15-Dec-04	60320410.4	16-Apr-08	MAGNETIC SHIELDING FOR ELECTRONIC CIRCUITS WHICH INCLUDE MAGNETIC MATERIALS
FILED	CR01-035	JAPA	2004-517676	18-Jun-03	24-Dec-04			MAGNETIC SHIELDING FOR ELECTRONIC CIRCUITS WHICH INCLUDE MAGNETIC MATERIALS
FILED	CR01-035	KORS	10-2004-7021344	18-Jun-03	27-Dec-04			MAGNETIC SHIELDING FOR ELECTRONIC CIRCUITS WHICH INCLUDE MAGNETIC MATERIALS
GRANTED	CR01-035	TAIW	092117676	27-Jun-03		I278277	01-Apr-07	MAGNETIC SHIELDING FOR ELECTRONIC CIRCUITS WHICH INCLUDE MAGNETIC MATERIALS
GRANTED	CR01-035	USA	10/184536	28-Jun-02		6936763	30-Aug-05	MAGNETIC SHIELDING FOR ELECTRONIC CIRCUITS WHICH INCLUDE MAGNETIC MATERIALS
FILED	CR01-038	CHIN	03814154.X	04-Jun-03	17-Dec-04			MAGNETORESISTIVE RANDOM ACCESS MEMORY WITH REDUCED SWITCHING FIELD
FILED	CR01-038	EPC	03731532.2	04-Jun-03	09-Dec-04			MAGNETORESISTIVE RANDOM ACCESS MEMORY WITH REDUCED SWITCHING FIELD
FILED	CR01-038	JAPA	2004-514080	04-Jun-03	04-Jun-03			MAGNETORESISTIVE RANDOM ACCESS MEMORY WITH REDUCED SWITCHING FIELD
FILED	CR01-038	KORS	10-2004-7020624	04-Jun-03	17-Dec-04			MAGNETORESISTIVE RANDOM ACCESS MEMORY WITH REDUCED SWITCHING FIELD
GRANTED	CR01-038	USA	10/173907	18-Jun-02		6633498	14-Oct-03	MAGNETORESISTIVE RANDOM ACCESS MEMORY WITH REDUCED SWITCHING FIELD
GRANTED	CR94-100	USA	08/711751	10-Sep-96		5734605	31-Mar-98	MULTI-LAYER MAGNETIC TUNNELING JUNCTION MEMORY CELLS
GRANTED	CR94-100	USA	09/028426	24-Feb-98		5978257	02-Nov-99	MULTI-LAYER MAGNETIC TUNNELING JUNCTION MEMORY CELLS
GRANTED	CR95-120	JAPA	8-326133	21-Nov-96		3831461	21-Jul-06	MAGNETIC MEMORY AND METHOD THE REFOR
GRANTED	CR95-120	KORS	10-1996-0033827	16-Aug-96		424962	17-Mar-04	MAGNETIC MEMORY AND METHOD THE REFOR
GRANTED	CR95-120	USA	08/562482	24-Nov-95		5659499	19-Aug-97	MAGNETIC MEMORY AND METHOD THE REFOR
GRANTED	CR95-149	JAPA	H8-305897	30-Oct-96		3673347	28-Apr-05	FERROMAGNETIC GMR MATERIAL
GRANTED	CR95-149	KORS	10-1996-0052210	06-Nov-96		397246	26-Aug-03	FERROMAGNETIC GMR MATERIAL AND METHODS OF FORMING AND USING
GRANTED	CR95-149	USA	08/553933	06-Nov-95		5702831	30-Dec-97	FERROMAGNETIC GMR MATERIAL
GRANTED	CR95-149	USA	08/932400	17-Sep-97		6177204	23-Jan-01	FERROMAGNETIC GMR MATERIAL
GRANTED	CR95-150	USA	08/723438	07-Oct-96		5861328	19-Jan-99	METHOD OF FABRICATING GMR DEVI CES
GRANTED	CR95-177	USA	08/646897	08-May-96		5703805	30-Dec-97	METHOD FOR DETECTING INFORMATION STORED IN A MRAM CELL HAVING TWO LAYERS IN DIFFERENT THICKNESSES

FILED	CR95-178	GERM	P19726852.8	24-Jun-97			A MAGNETIC RANDOM ACCESS MEMOR Y HAVING STACKED MEMORY CELLS AND FABRICATION METHOD THEREFO R
FILED	CR95-178	JAPA	9-231784	13-Aug-97			A MAGNETIC RANDOM ACCESS MEMOR Y HAVING STACKED MEMORY CELLS AND FABRICATION METHOD THEREFO R
GRANTED	CR95-178	USA	08/702781	23-Aug-96	5920500	06-Jul-99	A MAGNETIC RANDOM ACCESS MEMOR Y HAVING STACKED MEMORY CELLS AND FABRICATION METHOD THEREFO R
GRANTED	CR95-186	FRAN	99930749.9	25-Jun-99	EP1108257	14-Feb-07	MRAM CELL REQUIRING LOW SWITCHING FIELD
GRANTED	CR95-186	GBRI	99930749.9	25-Jun-99	EP1108257	14-Feb-07	MRAM CELL REQUIRING LOW SWITCHING FIELD
GRANTED	CR95-186	GERM	99930749.9	25-Jun-99	69935148.0	14-Feb-07	MRAM CELL REQUIRING LOW SWITCHING FIELD
FILED	CR95-186	JAPA	2001-506554	25-Jun-99			AN MRAM CELL REQUIRING LOW SWITCHING FIELD
GRANTED	CR95-186	SING	200101055-2	25-Jun-99	79313	31-Mar-04	MRAM CELL REQUIRING LOW SWITCHING FIELD
GRANTED	CR95-186	USA	08/862898	23-May-97	5917749	29-Jun-99	MRAM CELL REQUIRING LOW SWITCH ING FIELD
FILED	CR95-188	GERM	P19726077.2	19-Jun-97			A MEMORY CELL STRUCTURE IN A MAGNETIC RANDOM ACCESS MEMORY A ND A METHOD FOR FABRICATING TH EREOF
FILED	CR95-188	JAPA	9-191829	01-Jul-97			A MEMORY CELL STRUCTURE IN A M AGNETIC RANDOM ACCESS MEMORY A ND A METHOD FOR FABRICATING TH EREOF
GRANTED	CR95-188	USA	08/674387	02-Jul-96	5732016	24-Mar-98	A MEMORY CELL STRUCTURE IN A M AGNETIC RANDOM ACCESS MEMORY A ND A METHOD FOR FABRICATING TH EREOF
GRANTED	CR96-009	USA	08/709589	09-Sep-96	5745408	28-Apr-98	MULTI-LAYER MAGNETIC MEMORY CE LL WITH LOW SWITCHING CURRENT
GRANTED	CR96-039	USA	08/723159	25-Sep-96	5768183	16-Jun-98	MULTI-LAYER MAGNETIC MEMORY CE LLS WITH IMPROVED SWITCHING CH ARACTERISTICS
GRANTED	CR96-080	USA	08/767240	13-Dec-96	5734606	31-Mar-98	A MULTI-PIECE CELL AND A MRAM ARRAY INCLUDING THE CELL
GRANTED	CR96-192	USA	08/766637	13-Dec-96	5748519	05-May-98	A METHOD OF SELECTING A MEMORY CELL IN A MAGNETIC RANDOM ACC ESS MEMORY DEVICE
GRANTED	CR96-203	USA	08/892641	15-Jul-97	5818316	06-Oct-98	NONVOLATILE PROGRAMMABLE SWITC H
FILED	CR96-218	JAPA	10-533157	03-Feb-98			MRAM WITH ALIGNED MAGNETIC VECTORS
GRANTED	CR96-218	USA	08/795488	05-Feb-97	5757695	26-May-98	MRAM WITH ALIGNED MAGNETIC VEC TORS
GRANTED	CR96-262	USA	08/806275	25-Feb-97	5902690	11-May-99	STRAY MAGNETIC SHIELDING FOR A NON-VOLATILE MRAM

GRANTED	CR97-003	USA	08/874436	16-Jun-97	5838608	17-Nov-98	MULTI-LAYER MAGNETIC RANDOM AC CESS MEMORY AND METHOD FOR FAB RICATING THEREOF
GRANTED	CR97-004	USA	08/834968	07-Apr-97	5768181	16-Jun-98	MAGNETIC DEVICE HAVING MULTI-L AYER WITH INSULATING AND CONDU CTIVE LAYERS
GRANTED	CR97-084	USA	08/949605	14-Oct-97	5831920	03-Nov-98	GRM DEVICE HAVING A SENSE AMPL IFIER PROTECTED BY A CIRCUIT F OR DISSIPATING ELECTRIC CHARGE S
GRANTED	CR97-132	TAIW	89101560	31-Jan-00	NI-141711	01-Oct-01	MAGNETIC MEMORY UNIT HAVING FO UR STATES AND OPERATING METHOD THEREOF
GRANTED	CR97-132	USA	09/031195	26-Feb-98	5930164	27-Jul-99	MAGNETIC MEMORY UNIT HAVING FO UR STATES AND OPERATING METHOD THEREOF
GRANTED	CR97-133	TAIW	88114830	28-Jan-00	NI-145370	01-Dec-01	MAGNETIC RANDOM ACCESS MEMORY AND FABRICATING METHOD THEREOF
GRANTED	CR97-133	USA	09/144686	31-Aug-98	5940319	17-Aug-99	MAGNETIC RANDOM ACCESS MEMORY AND FABRICATING METHOD THEREOF
GRANTED	CR97-133	USA	09/339460	24-Jun-99	6174737	16-Jan-01	MAGNETIC RANDOM ACCESS MEMORY AND FABRICATING METHOD THEREOF
GRANTED	CR97-134	TAIW	89101561	29-Jan-00	NI-144644	21-Nov-01	SYMMETRIC MAGNETIC TUNNEL DEVI CE
GRANTED	CR97-134	USA	09/032107	27-Feb-98	6211559	03-Apr-01	SYMMETRIC MAGNETIC TUNNEL DEVI CE
GRANTED	CR97-139	USA	08/998366	24-Dec-97	5852574	22-Dec-98	HIGH DENSITY MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE AN D OPERATING METHOD THEREOF
GRANTED	CR97-145	TAIW	88119960	16-Nov-99	NI-141697	01-Oct-01	LOW SWITCHING FIELD MAGNETORES ISTIVE TUNNELING JUNCTION FOR HIGH DENSITY ARRAYS
GRANTED	CR97-145	USA	08/993768	18-Dec-97	5966323	12-Oct-99	LOW SWITCHING FIELD MAGNETORES ISTIVE TUNNELING JUNCTION FOR HIGH DENSITY ARRAYS
GRANTED	CR97-152	TAIW	89101770	02-Feb-00	NI-143884	01-Nov-01	MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE AND OPERATING M ETHOD THEREOF
GRANTED	CR97-152	USA	09/055731	07-Apr-98	5986925	16-Nov-99	MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE AND OPERATING M ETHOD THEREOF
GRANTED	CR97-158	USA	08/986764	08-Dec-97	6024885	15-Feb-00	PROCESS OF PATTERNING MAGNETIC FILMS
GRANTED	CR97-163	USA	08/993996	18-Dec-97	5959880	28-Sep-99	LOW ASPECT RATIO MAGNETORESIST IVE TUNNELING JUNCTION
FILED	CR98-033	JAPA	2000-562907	19-Jul-99			METHOD TO WRITE/READ MRAM ARRAYS
GRANTED	CR98-033	SING	200000800-3	15-Feb-00	97139	30-Sep-04	METHOD TO WRITE/READ MRAM ARRA YS
GRANTED	CR98-033	TAIW	88112617	27-Jan-00	NI-142530	11-Oct-01	METHOD TO WRITE/READ MRAM ARRA YS
GRANTED	CR98-033	USA	09/122722	27-Jul-98	6081445	27-Jun-00	METHOD TO WRITE/READ MRAM ARRA YS

FILED	CR98-035	JAPA	2000-560620	15-Jul-99			METHOD OF FABRICATING AN MTJ WITH LOW AREAL RESISTANCE
GRANTED	CR98-035	KORS	10-2000-7001870	15-Jul-99	605047	19-Jul-06	METHOD OF FABRICATING AN MTJ WITH LOW AREAL RESISTANCE
GRANTED	CR98-035	SING	200001392-0	15-Jul-99	71617	30-Apr-03	FABRICATING AN MTJ WITH LOW AREAL RESISTANCE
GRANTED	CR98-035	TAIW	88112224	18-Jan-00	NI-146399	11-Dec-01	METHOD OF FABRICATING AN MTJ W ITH LOW AREAL RESISTANCE
GRANTED	CR98-035	USA	09/119326	20-Jul-98	6083764	04-Jul-00	METHOD OF FABRICATING AN MTJ W ITH LOW AREAL RESISTANCE
FILED	CR98-036	JAPA	2000-560586	19-Jul-99			LOW SWITCHING FIELD MAGNETIC TUNNELING JUNCTION
GRANTED	CR98-036	SING	200001393-8	19-Jul-99	71618	30-May-03	LOW SWITCHING FIELD MAGNETIC T UNNELING JUNCTION FOR HIGH DEN SITY ARRAYS
GRANTED	CR98-036	USA	09/118979	20-Jul-98	5953248	14-Sep-99	LOW SWITCHING FIELD MAGNETIC T UNNELING JUNCTION FOR HIGH DEN SITY ARRAYS
FILED	CR98-038	JAPA	2000-560585	15-Jul-99			MRAM WITH SHARED WORD AND DIGIT LINES
GRANTED	CR98-038	SING	200001390-4	15-Jul-99	71615	31-Mar-03	MRAM WITH SHARED WORD AND DIGIT LINES
GRANTED	CR98-038	USA	09/118977	20-Jul-98	5946227	31-Aug-99	LOW SWITCHING FIELD MAGNETIC TUNNELING JUNCTION FOR HIGH DENSITY ARRAYS
FILED	CR98-062	JAPA	2000-564205	03-Aug-99			MRAM ARRAY HAVING A PLURALITY OF MEMORY BANKS
GRANTED	CR98-062	SING	200100533-9	03-Aug-99	78823	20-Mar-03	MRAM ARRAY HAVING A PLURALITY OF MEMORY BANKS
GRANTED	CR98-062	TAIW	88113174	16-Nov-99	NI-140201	11-Sep-01	MAGNETIC RANDOM ACCESS MEMORY ARRAY DIVIDED INTO A PLURALITY OF MEMORY BANKS
GRANTED	CR98-062	USA	09/128020	03-Aug-98	6111781	29-Aug-00	MAGNETIC RANDOM ACCESS MEMORY ARRAY DIVIDED INTO A PLURALITY OF MEMORY BANKS
GRANTED	CR98-062	USA	09/568822	10-May-00	6278631	21-Aug-01	MAGNETIC RANDOM ACCESS MEMORY ARRAY DIVIDED INTO A PLURALITY OF MEMORY BANKS
GRANTED	CR98-083	SING	200003998-2	13-Dec-99	74831	30-Apr-04	MAGNETIC RANDOM ACCESS MEMORY WITH A REFERENCE MEMORY ARRAY
GRANTED	CR98-083	USA	09/215386	18-Dec-98	6055178	25-Apr-00	MAGNETIC RANDOM ACCESS MEMORY WITH A REFERENCE MEMORY ARRAY
GRANTED	CR98-084	CHIN	00131425.4	18-Oct-00	ZL00131425.4	15-Feb-06	EMBEDDED MRAMS INCLUDING DUAL READ PORTS
FILED	CR98-084	JAPA	2000-316982	17-Oct-00			EMBEDDED MRAMS INCLUDING DUAL READ PORTS
GRANTED	CR98-084	KORS	2000-0057288	29-Sep-00	751841	17-Aug-07	EMBEDDED MRAMS INCLUDING DUAL READ

							PORTS
GRANTED	CR98-084	SING	200005661-4	03-Oct-00	90176	30-Apr-04	EMBEDDED MRAMS INCLUDING DUAL READ PORTS
GRANTED	CR98-084	TAIW	89120907	06-Oct-00	NI-152156	21-Mar-02	EMBEDDED MRAMS INCLUDING DUAL READ PORTS
GRANTED	CR98-084	USA	09/420122	19-Oct-99	6609174	19-Aug-03	EMBEDDED MRAMS INCLUDING DUAL READ PORTS
GRANTED	CR98-102	SING	200004644-1	13-Dec-99	75332	31-Jul-03	METHOD OF FABRICATING A MAGNET IC RANDOM ACCESS MEMORY
GRANTED	CR98-102	TAIW	88122405	20-Dec-99	NI-141992	01-Oct-01	METHOD OF FABRICATING A MAGNET IC RANDOM ACCESS MEMORY
GRANTED	CR98-102	USA	09/216821	21-Dec-98	6153443	28-Nov-00	METHOD OF FABRICATING A MAGNET IC RANDOM ACCESS MEMORY
FILED	CR99-001	JAPA	2000-190486	26-Jun-00			MAGNETIC ELEMENT WITH IMPROVED FIELD RESPONSE AND FABRICATING METHOD THEREOF
GRANTED	CR99-001	USA	09/356864	19-Jul-99	6292389	18-Sep-01	MAGNETIC ELEMENT WITH IMPROVED FIELD RESPONSE AND FABRICATING METHOD THEREOF
GRANTED	CR99-001	USA	09/825705	05-Apr-01	6376260	23-Apr-02	MAGNETIC ELEMENT WITH IMPROVED FIELD RESPONSE AND FABRICATING METHOD THEREOF
GRANTED	CR99-007	FRAN	00110548.5	17-May-00	EP1054449	13-Dec-06	MAGNETIC RANDOM ACCESS MEMORY AND FABRICATING METHOD THEREOF
GRANTED	CR99-007	GBRI	00110548.5	17-May-00	EP1054449	13-Dec-06	MAGNETIC RANDOM ACCESS MEMORY AND FABRICATING METHOD THEREOF
GRANTED	CR99-007	GERM	00110548.5	17-May-00	60032281.5	13-Dec-06	MAGNETIC RANDOM ACCESS MEMORY AND FABRICATING METHOD THEREOF
FILED	CR99-007	JAPA	2000-122085	24-Apr-00			MAGNETIC RANDOM ACCESS MEMORY AND FABRICATING METHOD THEREOF
GRANTED	CR99-007	USA	09/312833	17-May-99	6165803	26-Dec-00	MAGNETIC RANDOM ACCESS MEMORY AND FABRICATING METHOD THEREOF
GRANTED	CR99-012	CHIN	00131625.7	20-Oct-00	ZL00131625.7	09-Mar-05	MAGNETIC ELEMENT WITH IMPROVED FIELD RESPONSE AND FABRICATING METHOD THEREOF
FILED	CR99-012	JAPA	2000-317501	18-Oct-00			MAGNETIC ELEMENT WITH IMPROVED FIELD RESPONSE AND FABRICATING METHOD THEREOF
GRANTED	CR99-012	KORS	10-2000-0058911	06-Oct-00	807295	19-Feb-08	MAGNETIC ELEMENT WITH IMPROVED FIELD RESPONSE AND FABRICATING METHOD THEREOF
GRANTED	CR99-012	SING	200005854-5	13-Oct-00	87185	31-Jul-02	MAGNETIC ELEMENT WITH IMPROVED FIELD RESPONSE AND FABRICATING METHOD THEREOF
GRANTED	CR99-012	TAIW	89120549	03-Oct-00	NI-161016	11-Aug-02	MAGNETIC ELEMENT WITH IMPROVED FIELD

								RESPONSE AND FABRICATING METHOD THEREOF
								MAGNETIC ELEMENT WITH IMPROVED FIELD RESPONSE AND FABRICATING METHOD THEREOF
GRANTED	CR99-012	USA	09/422447	21-Oct-99		6205052	20-Mar-01	
GRANTED	CR99-018	CHIN	00135059.5	07-Dec-00		ZL00135059.5	27-Apr-05	MTJ STACKED CELL MEMORY SENSING METHOD AND APPARATUS
FILED	CR99-018	JAPA	2000-374139	08-Dec-00				MTJ STACKED CELL MEMORY SENSING METHOD AND APPARATUS
GRANTED	CR99-018	KORS	10-2000-0073749	06-Dec-00		798092	18-Jan-08	MTJ STACKED CELL MEMORY SENSING METHOD AND APPARATUS
GRANTED	CR99-018	SING	200007283-5	08-Dec-00		91315	14-Nov-02	MTJ STACKED CELL MEMORY SENSING METHOD AND APPARATUS
GRANTED	CR99-018	TAIW	89124537	20-Nov-00		NI-155784	21-May-02	MTJ STACKED CELL MEMORY SENSING METHOD AND APPARATUS
GRANTED	CR99-018	USA	09/456615	08-Dec-99		6169689	02-Jan-01	MTJ STACKED CELL MEMORY SENSING METHOD AND APPARATUS
GRANTED	CR99-021	CHIN	00135254.7	12-Dec-00		ZL00135254.7	04-May-05	MRAM HAVING SEMICONDUCTOR DEVICE INTEGRATED THEREIN
FILED	CR99-021	JAPA	2000-361340	28-Nov-00				MRAM HAVING SEMICONDUCTOR DEVICE INTEGRATED THEREIN
GRANTED	CR99-021	SING	200007284-3	08-Dec-00		88806	29-Oct-04	MRAM HAVING SEMICONDUCTOR DEVICE INTEGRATED THEREIN
GRANTED	CR99-021	TAIW	89124414	17-Nov-00		NI-154661	01-May-02	MRAM HAVING SEMICONDUCTOR DEVICE INTEGRATED THEREIN
GRANTED	CR99-021	USA	09/460056	13-Dec-99		6285581	04-Sep-01	MRAM HAVING SEMICONDUCTOR DEVICE INTEGRATED THEREIN
FILED	CR99-023	EPC	01922513.5	21-Mar-01	16-Sep-02			MULTI-LAYER TUNNELING DEVICE WITH A GRADED STOICHIOMETRY INSULATING LAYER
FILED	CR99-023	FRAN	01922513.5	21-Mar-01	16-Sep-02			MULTI-LAYER TUNNELING DEVICE WITH A GRADED STOICHIOMETRY INSULATING LAYER
FILED	CR99-023	GBRI	01922513.5	21-Mar-01	16-Sep-02			MULTI-LAYER TUNNELING DEVICE WITH A GRADED STOICHIOMETRY INSULATING LAYER
FILED	CR99-023	GERM	01922513.5	21-Mar-01	16-Sep-02			MULTI-LAYER TUNNELING DEVICE WITH A GRADED STOICHIOMETRY INSULATING LAYER
FILED	CR99-023	JAPA	2001-569831	21-Mar-01				MULTI-LAYER TUNNELING DEVICE WITH A GRADED STOICHIOMETRY INSULATING LAYER
FILED	CR99-023	KORS	10-2002-7012462	21-Mar-01				MULTI-LAYER TUNNELING DEVICE WITH A GRADED STOICHIOMETRY INSULATING LAYER

GRANTED	CR99-023	SING	200205745-3	21-Mar-01	18-Sep-02	91990	08-Jan-03	MULTI-LAYER TUNNELING DEVICE WITH A GRADED STOICHIOMETRY INSULATING LAYER
GRANTED	CR99-023	TAIW	90106537	21-Mar-01		NI-158350	01-Jul-02	MULTI-LAYER TUNNELING DEVICE WITH A GRADED STOICHIOMETRY INSULATING LAYER
GRANTED	CR99-023	USA	09/532572	22-Mar-00		6281538	28-Aug-01	MULTI-LAYER TUNNELING DEVICE WITH A GRADED STOICHIOMETRY INSULATING LAYER
GRANTED	CR99-023	USA	09/894368	27-Jun-01		6395595	28-May-02	MULTI-LAYER TUNNELING DEVICE WITH A GRADED STOICHIOMETRY INSULATING LAYER
FILED	CR99-024	CHIN	200410064116.8	15-Dec-00	15-Dec-00			MAGNETIC ELEMENT WITH DUAL MAGNETIC STATES AND FABRICATING METHOD THEREOF
GRANTED	CR99-024	CHIN	00136605.X	15-Dec-00		ZL00136605.X	13-Oct-04	MAGNETIC ELEMENT WITH DUAL MAGNETIC STATES AND FABRICATING METHOD THEREOF
FILED	CR99-024	HONG	05107283.6	22-Aug-05	15-Dec-00			MAGNETIC ELEMENT WITH DUAL MAGNETIC STATES AND FABRICATING METHOD THEREOF
FILED	CR99-024	JAPA	2000-383163	18-Dec-00				MAGNETIC ELEMENT WITH DUAL MAGNETIC STATES AND FABRICATING METHOD THEREOF
GRANTED	CR99-024	KORS	10-2000-0075640	12-Dec-00		748069	03-Aug-07	MAGNETIC ELEMENT WITH DUAL MAGNETIC STATES AND FABRICATING METHOD THEREOF
GRANTED	CR99-024	SING	200007285-0	08-Dec-00		87195	31-Aug-04	MAGNETIC ELEMENT WITH DUAL MAGNETIC STATES AND FABRICATING METHOD THEREOF
GRANTED	CR99-024	TAIW	89125412	30-Nov-00		NI-154553	01-May-02	MAGNETIC ELEMENT WITH DUAL MAGNETIC STATES AND FABRICATING METHOD THEREOF
GRANTED	CR99-024	USA	09/464807	17-Dec-99		6233172	15-May-01	MAGNETIC ELEMENT WITH DUAL MAGNETIC STATES AND FABRICATING METHOD THEREOF
GRANTED	CR99-027	FRAN	01928727.5	20-Apr-01	25-Oct-02	EP1279176	30-May-07	MAGNETIC ELEMENT WITH INSULATING VEILS AND FABRICATING METHOD THEREOF
GRANTED	CR99-027	GBRI	01928727.5	20-Apr-01	25-Oct-02	EP1279176	30-May-07	MAGNETIC ELEMENT WITH INSULATING VEILS AND FABRICATING METHOD THEREOF
GRANTED	CR99-027	GERM	01928727.5	20-Apr-01	25-Oct-02	60128678.2	30-May-07	MAGNETIC ELEMENT WITH INSULATING VEILS AND FABRICATING METHOD THEREOF
FILED	CR99-027	JAPA	2001-581295	20-Apr-01				MAGNETIC ELEMENT WITH INSULATING VEILS AND FABRICATING METHOD THEREOF
FILED	CR99-027	KORS	10-2002-7014490	20-Apr-01				MAGNETIC ELEMENT WITH INSULATING VEILS AND FABRICATING METHOD THEREOF

GRANTED	CR99-027	TAIW	90108916	13-Apr-01		NI-163849	01-Oct-02	MAGNETIC ELEMENT WITH INSULATING VEILS AND FABRICATING METHOD THEREOF
GRANTED	CR99-027	USA	10/349702	22-Jan-03		6835423	28-Dec-04	MAGNETIC ELEMENT WITH INSULATING VEILS AND FABRICATING METHOD THEREOF
GRANTED	CR99-027	USA	10/830264	21-Apr-04		6912107	28-Jun-05	MAGNETIC ELEMENT WITH INSULATING VEILS AND FABRICATING METHOD THEREOF
FILED	CR99-034	EPC	01920594.7	21-Mar-01	16-Sep-02			METHOD OF FABRICATING FLUX CONCENTRATING LAYER FOR USE WITH MAGNETORESISTIVE RANDOM ACCESS MEMORIES
FILED	CR99-034	JAPA	2001-569859	21-Mar-01				METHOD OF FABRICATING FLUX CONCENTRATING LAYER FOR USE WITH MAGNETORESISTIVE RANDOM ACCESS MEMORIES
GRANTED	CR99-034	KORS	10-2002-7012470	21-Mar-01		801455	30-Jan-08	METHOD OF FABRICATING FLUX CONCENTRATING LAYER FOR USE WITH MAGNETORESISTIVE RANDOM ACCESS MEMORIES
GRANTED	CR99-034	SING	200205732-1	21-Mar-01	18-Sep-02	91980	30-Jun-05	METHOD OF FABRICATING FLUX CONCENTRATING LAYER FOR USE WITH MAGNETORESISTIVE RANDOM ACCESS MEMORIES
GRANTED	CR99-034	TAIW	90106479	20-Mar-01		NI-157693	21-Jun-02	METHOD OF FABRICATING FLUX CONCENTRATING LAYER FOR USE WITH MAGNETORESISTIVE RANDOM ACCESS MEMORIES
GRANTED	CR99-034	USA	09/528971	21-Mar-00		6211090	03-Apr-01	METHOD OF FABRICATING FLUX CONCENTRATING LAYER FOR USE WITH MAGNETORESISTIVE RANDOM ACCESS MEMORIES
FILED	CR99-035	JAPA	2001-573483	29-Mar-01				CURRENT CONVEYOR AND METHOD FOR READOUT OF MTJ MEMORIES
GRANTED	CR99-035	KORS	10-2002-7013047	29-Mar-01		785259	06-Dec-07	CURRENT CONVEYOR AND METHOD FOR READOUT OF MTJ MEMORIES
GRANTED	CR99-035	TAIW	90107598	07-May-01		NI-157700	21-Jun-02	CURRENT CONVEYOR AND METHOD FOR READOUT OF MTJ MEMORIES
GRANTED	CR99-035	USA	09/540794	31-Mar-00		6205073	20-Mar-01	CURRENT CONVEYOR AND METHOD FOR READOUT OF MTJ MEMORIES
FILED	CR99-036	CHIN	01814496.9	09-Aug-01	21-Feb-03			METHOD OF FABRICATING THERMALLY STABLE MTJ CELL AND APPARATUS
FILED	CR99-036	JAPA	2002-521374	09-Aug-01				METHOD OF FABRICATING THERMALLY STABLE MTJ CELL AND APPARATUS
FILED	CR99-036	KORS	10-2003-7002575	09-Aug-01				METHOD OF FABRICATING THERMALLY STABLE MTJ CELL AND APPARATUS
GRANTED	CR99-036	TAIW	90120379	20-Aug-01		NI-169821	07-May-03	METHOD OF FABRICATING THERMALLY STABLE MTJ CELL AND APPARATUS

GRANTED	CR99-036	USA	09/642350	21-Aug-00		6544801	08-Apr-03	METHOD OF FABRICATING THERMALLY STABLE MTJ CELL AND APPARATUS
FILED	CR99-037	JAPA	2001-569832	22-Mar-01				MAGNETIC ELEMENT WITH AN IMPROVED MAGNETORESISTANCE RATIO
GRANTED	CR99-037	KORS	10-2002-7012400	22-Mar-01		801452	30-Jan-08	MAGNETIC ELEMENT WITH AN IMPROVED MAGNETORESISTANCE RATIO
GRANTED	CR99-037	SING	200205746-1	22-Mar-01	18-Sep-02	91991	31-Aug-07	MAGNETIC ELEMENT WITH AN IMPROVED MAGNETORESISTANCE RATIO
GRANTED	CR99-037	TAIW	90106612	21-Mar-01		I264739	21-Oct-06	MAGNETIC ELEMENT WITH AN IMPROVED MAGNETORESISTANCE RATIO AND FABRICATING METHOD THEREOF
GRANTED	CR99-037	USA	09/532721	22-Mar-00		6469926	22-Oct-02	MAGNETIC ELEMENT WITH AN IMPROVED MAGNETORESISTANCE RATIO AND FABRICATING METHOD THEREOF
GRANTED	CR99-037	USA	10/224253	20-Aug-02		6750068	15-Jun-04	MAGNETIC ELEMENT WITH AN IMPROVED MAGNETORESISTANCE RATIO AND FABRICATING METHOD THEREOF
FILED	MT10037TS	USA	11/438541	22-May-06				NON-VOLATILE MEMORY CELL AND METHODS THEREOF
FILED	MT10038TS	PCT	PCT/US2007/065616	30-Mar-07				SENSE AMPLIFIER WITH MULTIPLE BITS SHARING A COMMON REFERENCE
FILED	MT10038TS	TAIW	096112728	11-Apr-07				SENSE AMPLIFIER WITH MULTIPLE BITS SHARING A COMMON REFERENCE
GRANTED	MT10038TS	USA	11/422774	07-Jun-06		7292484	06-Nov-07	SENSE AMPLIFIER WITH MULTIPLE BITS SHARING A COMMON REFERENCE
FILED	MT10149ZP	PCT	PCT/US2007/079698	27-Sep-07				MAGNETIC TUNNEL JUNCTION STRUCTURE AND METHOD
FILED	MT10149ZP	TAIW	096137717	08-Oct-07				MAGNETIC TUNNEL JUNCTION STRUCTURE AND METHOD
FILED	MT10149ZP	USA	11/601129	15-Nov-06				MAGNETIC TUNNEL JUNCTION STRUCTURE AND METHOD
FILED	MT10154ZP	USA	11/444089	31-May-06				MRAM SYNTHETIC ANTIFEROMAGNET STRUCTURE
FILED	MT10245ZP	USA	11/511691	28-Aug-06				SPIN-TRANSFER BASED MRAM WITH REDUCED CRITICAL CURRENT DENSITY
FILED	MT10269ZP	USA	11/590276	30-Oct-06				ELECTRONIC ASSEMBLY HAVING MAGNETIC TUNNEL JUNCTION VOLTAGE SENSORS AND METHOD FOR FORMING SAME
FILED	MT10270ZP	USA	11/584473	19-Oct-06				MAGNETIC TUNNEL JUNCTION SENSOR WITH MOVEABLE CLADDING
FILED	MT10304ZP	PCT	PCT/US2007/077171	30-Aug-07				MAGNETIC TUNNEL JUNCTION MEMORY AND METHOD WITH ETCH-STOP LAYER
FILED	MT10304ZP	TAIW	096133598	07-Sep-07				MAGNETIC TUNNEL JUNCTION MEMORY AND METHOD WITH ETCH-STOP LAYER
FILED	MT10304ZP	USA	11/584411	19-Oct-06				MAGNETIC TUNNEL JUNCTION MEMORY AND

							METHOD WITH ETCH-STOP LAYER
FILED	MT10311ZP	USA	11/755498	30-May-07			MAGNETOELECTRONIC DEVICE HAVING ENHANCED PERMEABILITY DIELECTRIC AND METHOD OF MANUFACTURE
FILED	MT10325ZP	USA	11/739625	24-Apr-07			MAGNETORESISTIVE DEVICE AND METHOD OF PACKAGING SAME
FILED	MT10391ZP	USA	11/736960	18-Apr-07			SPIN-TRANSFER MRAM STRUCTURE AND METHODS
FILED	MT10400ZP	PCT	PCT/US2008/051844	24-Jan-08			MRAM MEMORY CONDITIONING
FILED	MT10400ZP	USA	11/678346	23-Feb-07			MRAM MEMORY CONDITIONING
FILED	MT10422ZP	USA	11/679982	28-Feb-07			MRAM FREE LAYER SYNTHETIC ANTIFERROMAGNET STRUCTURE AND METHODS
FILED	MT10430ZP	USA	11/689722	22-Mar-07			MRAM TUNNEL BARRIER STRUCTURE AND METHODS
FILED	MT10510ZP	USA	11/839044	15-Aug-07			METHODS AND APPARATUS FOR A SYNTHETIC ANTI-FERROMAGNET STRUCTURE WITH IMPROVED THERMAL STABILITY
FILED	MT10511ZP	USA	11/938816	13-Nov-07			METHODS AND STRUCTURES FOR EXCHANGE-COUPLED MAGNETIC MULTI-LAYER STRUCTURE WITH IMPROVED OPERATING TEMPERATURE BEHAVIOR
FILED	MT10513ZP	USA	11/740066	25-Apr-07			ENHANCED PERMEABILITY DEVICE STRUCTURES AND METHOD
FILED	MT10651ZP	USA	11/864409	28-Sep-07			ELECTRONIC DEVICE INCLUDING A MAGNETO-RESISTIVE MEMORY DEVICE AND A PROCESS FOR FORMING THE ELECTRONIC DEVICE
FILED	MT10679ZP	USA	11/848053	30-Aug-07			METHODS AND STRUCTURES FOR AN INTEGRATED TWO-AXIS MAGNETIC FIELD SENSOR
FILED	MT10743ZP	USA	11/870856	11-Oct-07			MAGNETIC ELEMENT HAVING REDUCED CURRENT DENSITY
FILED	MT10815ZP	USA	12/117396	08-May-08			TWO-AXIS MAGNETIC FIELD SENSOR WITH MULTIPLE PINNING DIRECTIONS
FILED	MT10822ZP	USA	12/055482	26-Mar-08			IMPROVED MAGNETIC SENSOR DESIGN FOR SUPPRESION OF BARKHAUSEN NOISE
FILED	MT10900ZP	USA	12/035011	21-Feb-08			MAGNETIC TUNNEL JUNCTION DEVICE
GRANTED	SC10553P	SING	200001391-2	15-Jul-99	71616	31-Jan-05	LOW RESISTANCE MTJ
GRANTED	SC10553P	USA	09/119537	20-Jul-98	6183859	06-Feb-01	LOW RESISTANCE MTJ
GRANTED	SC10553P	USA	09/639746	14-Aug-00	6261646	17-Jul-01	METHOD OF MAKING A LOW RESISTANCE MTJ
GRANTED	SC10977TC	USA	09/675204	29-Sep-00	6272040	07-Aug-01	SYSTEM AND METHOD FOR PROGRAMING A

								MAGNETORESISTIVE MEMORY DEVICE
GRANTED	SC10978TC	CHIN	01816541.9	13-Sep-01		ZL01816541.9	05-Apr-06	AN ANALOG FUNCTIONAL MODULE USING MAGNETORESISTIVE MEMORY TECHNOLOGY
FILED	SC10978TC	JAPA	2002-533308	13-Sep-01				AN ANALOG FUNCTIONAL MODULE USING MAGNETORESISTIVE MEMORY TECHNOLOGY
GRANTED	SC10978TC	KORS	10-2003-7004573	13-Sep-01		823049	11-Apr-08	AN ANALOG FUNCTIONAL MODULE USING MAGNETORESISTIVE MEMORY TECHNOLOGY
GRANTED	SC10978TC	USA	09/675202	29-Sep-00		6314020	06-Nov-01	AN ANALOG FUNCTIONAL MODULE USING MAGNETORESISTIVE MEMORY TECHNOLOGY
FILED	SC11036TH	JAPA	2001-30430	07-Feb-01				CHARGE CONSERVING WRITE METHOD AND SYSTEM FOR AN MRAM
GRANTED	SC11036TH	USA	09/546367	10-Apr-00		6215707	10-Apr-01	CHARGE CONSERVING WRITE METHOD AND SYSTEM FOR AN MRAM
GRANTED	SC11125TC	USA	09/675182	29-Sep-00		6252471	26-Jun-01	PROGRAMMABLE OSCILLATOR USING MAGNETORESISTIVE MEMORY TECHNOLOGY
GRANTED	SC11130TC	USA	09/675183	29-Sep-00		6476753	05-Nov-02	AN ANALOG TO DIGITAL CONVERTER USING MAGNETORESISTIVE MEMORY TECHNOLOGY
GRANTED	SC11217TC	USA	09/675203	29-Sep-00		6252795	26-Jun-01	PROGRAMMABLE RESISTIVE CIRCUIT USING MAGNETORESISTIVE MEMORY TECHNOLOGY
GRANTED	SC11235TC	USA	09/675181	29-Sep-00		6225933	01-May-01	DIGITAL TO ANALOG CONVERTER USING MAGNETORESISTIVE MEMORY TECHNOLOGY
FILED	SC11251TP	CHIN	200610005094.7	08-Nov-01	15-Feb-06			SELF-ALIGNED MAGNETIC CLAD WRITE LINE AND METHOD THEREOF
GRANTED	SC11251TP	CHIN	01820458.9	08-Nov-01		ZL01820458.9	28-Jun-06	SELF-ALIGNED MAGNETIC CLAD WRITE LINE AND METHOD THEREOF
FILED	SC11251TP	JAPA	2002-543677	08-Nov-01				SELF-ALIGNED MAGNETIC CLAD WRITE LINE AND METHOD THEREOF
GRANTED	SC11251TP	KORS	10-2003-7006612	08-Nov-01		823465	14-Apr-08	SELF-ALIGNED MAGNETIC CLAD WRITE LINE AND METHOD THEREOF
GRANTED	SC11251TP	TAIW	90128203	14-Nov-01		NI-171924	10-Jun-03	SELF-ALIGNED MAGNETIC CLAD WRITE LINE AND ITS METHOD OF FORMATION
GRANTED	SC11251TP	USA	09/713734	15-Nov-00		6555858	29-Apr-03	SELF-ALIGNED MAGNETIC CLAD WRITE LINE AND ITS METHOD OF FORMATION
GRANTED	SC11251TP	USA	10/378348	03-Mar-03		6916669	12-Jul-05	SELF-ALIGNED MAGNETIC CLAD WRITE LINE AND ITS METHOD OF FORMATION
GRANTED	SC12001TP	USA	10/304625	26-Nov-02		6944052	13-Sep-05	MAGNETORESISTIVE RANDOM ACCESS MEMORY (MRAM) CELL HAVING A DIODE WITH ASYMMETRICAL CHARACTERISTICS
FILED	SC12011TC	CHIN	03815293.2	24-Apr-03	28-Dec-04			BALANCED LOAD MEMORY AND METHOF OF OPERATION
FILED	SC12011TC	JAPA	2004-517522	24-Apr-03	27-Dec-04			BALANCED LOAD MEMORY AND METHOF OF OPERATION
FILED	SC12011TC	KORS	10-2004-7021346	24-Apr-03	27-Dec-04			BALANCED LOAD MEMORY AND METHOF OF OPERATION
FILED	SC12011TC	TAIW	092117692	27-Jun-03				BALANCED LOAD MEMORY AND METHOD OF

								OPERATION
GRANTED	SC12011TC	USA	10/184720	28-Jun-02		6711068	23-Mar-04	BALANCED LOAD MEMORY AND METHOF OF OPERATION
FILED	SC12012TC	CHIN	03815295.9	29-Apr-03	28-Dec-04			CIRCUIT AND METHOD OF WRITING A TOGGLE MEMORY
GRANTED	SC12012TC	FRAN	03724302.9	29-Apr-03	15-Dec-04	EP1518246	12-Jul-06	CIRCUIT AND METHOD OF WRITING A TOGGLE MEMORY
GRANTED	SC12012TC	GBRI	03724302.9	29-Apr-03	15-Dec-04	EP1518246	12-Jul-06	CIRCUIT AND METHOD OF WRITING A TOGGLE MEMORY
GRANTED	SC12012TC	GERM	03724302.9	29-Apr-03	15-Dec-04	60306782.4	12-Jul-06	CIRCUIT AND METHOD OF WRITING A TOGGLE MEMORY
FILED	SC12012TC	JAPA	2004-517527	29-Apr-03	24-Dec-04			CIRCUIT AND METHOD OF WRITING A TOGGLE MEMORY
FILED	SC12012TC	KORS	10-2004-7021252	29-Apr-03	27-Dec-04			CIRCUIT AND METHOD OF WRITING A TOGGLE MEMORY
FILED	SC12012TC	TAIW	092117443	26-Jun-03				CIRCUIT AND METHOD OF WRITING A TOGGLE MEMORY
GRANTED	SC12012TC	USA	10/186141	28-Jun-02		6693824	17-Feb-04	CIRCUIT AND METHOD OF WRITING A TOGGLE MEMORY
FILED	SC12015TC	CHIN	03815272.X	29-Apr-03	28-Dec-04			MRAM ARCHITECTURE WITH ELECTRICALLY ISOLATED READ AND WRITE CIRCUITRY
FILED	SC12015TC	EPC	03726492.6	29-Apr-03	15-Dec-04			MRAM ARCHITECTURE WITH ELECTRICALLY ISOLATED READ AND WRITE CIRCUITRY
FILED	SC12015TC	JAPA	2004-517525	29-Apr-03	24-Dec-04			MRAM ARCHITECTURE WITH ELECTRICALLY ISOLATED READ AND WRITE CIRCUITRY
FILED	SC12015TC	KORS	10-2004-7021254	29-Apr-03	27-Dec-04			MRAM ARCHITECTURE WITH ELECTRICALLY ISOLATED READ AND WRITE CIRCUITRY
FILED	SC12015TC	TAIW	092117683	27-Jun-03				MRAM ARCHITECTURE WITH ELECTRICALLY ISOLATED READ AND WRITE CIRCUITRY
GRANTED	SC12015TC	USA	10/185868	28-Jun-02		6903964	07-Jun-05	MRAM ARCHITECTURE WITH ELECTRICALLY ISOLATED READ AND WRITE CIRCUITRY
GRANTED	SC12015TC	USA	11/076523	09-Mar-05		7154772	26-Dec-06	MRAM ARCHITECTURE WITH ELECTRICALLY ISOLATED READ AND WRITE CIRCUITRY
GRANTED	SC12065ZP	CHIN	200380104188.4	14-Nov-03	26-May-05	200380104188.4	01-Aug-07	CLADDED CONDUCTOR FOR USE IN A MAGNETOELECTRONICS DEVICE AND METHOD FOR FABRICATING THE SAME
FILED	SC12065ZP	JAPA	2004-557207	14-Nov-03	27-May-05			CLADDED CONDUCTOR FOR USE IN A MAGNETOELECTRONICS DEVICE AND METHOD FOR FABRICATING THE SAME
FILED	SC12065ZP	KORS	10-2005-7009385	14-Nov-03	25-May-05			CLADDED CONDUCTOR FOR USE IN A MAGNETOELECTRONICS DEVICE AND METHOD FOR FABRICATING THE SAME
FILED	SC12065ZP	PCT	PCT/US03/36561	14-Nov-03				CLADDED CONDUCTOR FOR USE IN A MAGNETOELECTRONICS DEVICE AND METHOD FOR FABRICATING THE SAME

FILED	SC12065ZP	TAIW	092133359	27-Nov-03				CLADDED CONDUCTOR FOR USE IN A MAGNETOELECTRONICS DEVICE AND METHOD FOR FABRICATING THE SAME
GRANTED	SC12065ZP	USA	10/306250	27-Nov-02		6885074	26-Apr-05	CLADDED CONDUCTOR FOR USE IN A MAGNETOELECTRONICS DEVICE AND METHOD FOR FABRICATING THE SAME
GRANTED	SC12065ZP	USA	11/082617	16-Mar-05		7105363	12-Sep-06	CLADDED CONDUCTOR FOR USE IN A MAGNETOELECTRONICS DEVICE AND METHOD FOR FABRICATING THE SAME
FILED	SC12079TP	CHIN	03820242.5	22-May-03	25-Feb-05			MAGNETIC RANDOM ACCESS MEMORY HAVING A VERTICAL WRITE LINE
FILED	SC12079TP	JAPA	2004-532568	22-May-03	25-Feb-05			MAGNETIC RANDOM ACCESS MEMORY HAVING A VERTICAL WRITE LINE
FILED	SC12079TP	KORS	10-2005-7003265	22-May-03	25-Feb-05			MAGNETIC RANDOM ACCESS MEMORY HAVING A VERTICAL WRITE LINE
GRANTED	SC12079TP	TAIW	092115413	06-Jun-03		I243377	11-Nov-05	MEMORY CELL AND METHOD FOR MAKING THE SAME, AND MEMORY DEVICE
GRANTED	SC12079TP	USA	10/228684	27-Aug-02		6621730	16-Sep-03	MAGNETIC RANDOM ACCESS MEMORY HAVING A VERTICAL WRITE LINE
GRANTED	SC12095TH	USA	10/230690	29-Aug-02		7170706	30-Jan-07	HARD DISK SYSTEM WITH NON-VOLATILE IC BASED MEMORY FOR STORING DATA
GRANTED	SC12099TC	USA	10/185075	28-Jun-02		6657889	02-Dec-03	MEMORY HAVING WRITE CURRENT RAMP RATE CONTROL
GRANTED	SC12158TC	USA	10/185566	28-Jun-02		6760266	06-Jul-04	SENSE AMPLIFIER AND METHOD FOR PERFORMING A READ OPERATION IN A MRAM
FILED	SC12159TC	JAPA	2004-517535	07-May-03	24-Dec-04			CIRCUIT AND METHOD FOR READING A TOGGLE MEMORY CELL
GRANTED	SC12159TC	TAIW	092117684	27-Jun-03		I289847	11-Nov-07	CIRCUIT AND METHOD FOR READING A TOGGLE MEMORY CELL
GRANTED	SC12159TC	USA	10/184811	28-Jun-02		6744663	01-Jun-04	CIRCUIT AND METHOD FOR READING A TOGGLE MEMORY CELL
FILED	SC12183ZP	CHIN	200380106467.4	20-Oct-03	17-Jun-05			METHOD FOR FABRICATING A FLUX CONCENTRATING SYSTEM FOR USE IN A MAGNETOELECTRONICS DEVICE
FILED	SC12183ZP	JAPA	2004-564801	20-Oct-03	31-May-05			METHOD FOR FABRICATING A FLUX CONCENTRATING SYSTEM FOR USE IN A MAGNETOELECTRONICS DEVICE
FILED	SC12183ZP	KORS	10-2005-7011006	20-Oct-03	15-Jun-05			METHOD FOR FABRICATING A FLUX CONCENTRATING SYSTEM FOR USE IN A MAGNETOELECTRONICS DEVICE
GRANTED	SC12183ZP	SING	200503035-8	20-Oct-03		112464	29-Sep-06	METHOD FOR FABRICATING A FLUX CONCENTRATING SYSTEM FOR USE IN A MAGNETOELECTRONICS DEVICE
FILED	SC12183ZP	TAIW	092136222	19-Dec-03				METHOD FOR FABRICATING A FLUX CONCENTRATING SYSTEM FOR USE IN A

								MAGNETOELECTRONICS DEVICE
GRANTED	SC12183ZP	USA	10/324716	19-Dec-02		6943038	13-Sep-05	METHOD FOR FABRICATING A FLUX CONCENTRATING SYSTEM FOR USE IN A MAGNETOELECTRONICS DEVICE
GRANTED	SC12183ZP	USA	11/125955	09-May-05		7279341	09-Oct-07	METHOD FOR FABRICATING A FLUX CONCENTRATING SYSTEM FOR USE IN A MAGNETOELECTRONICS DEVICE
GRANTED	SC12214TC	USA	10/185888	28-Jun-02		6714440	30-Mar-04	MEMORY ARCHITECTURE WITH WRITE CIRCUITRY AND METHOD THEREFOR
FILED	SC12217TC	JAPA	2004-517531	01-May-03	24-Dec-04			MEMORY HAVING A PRECHARGE CIRCUIT AND METHOD THEREFOR
GRANTED	SC12217TC	TAIW	092117670	27-Jun-03		I287233	21-Sep-07	MEMORY HAVING A PRECHARGE CIRCUIT AND METHOD THEREFOR
GRANTED	SC12217TC	USA	10/185488	28-Jun-02		6711052	23-Mar-04	MEMORY HAVING A PRECHARGE CIRCUIT AND METHOD THEREFOR
FILED	SC12259ZP	TAIW	092137153	26-Dec-03				MRAM AND METHODS FOR READING THE MRAM
GRANTED	SC12259ZP	USA	10/331058	27-Dec-02		6888743	03-May-05	MRAM ARCHITECTURE
GRANTED	SC12259ZP	USA	10/679134	02-Oct-03		6909631	21-Jun-05	MRAM AND METHODS FOR READING THE MRAM
GRANTED	SC12293ZK	USA	10/746014	23-Dec-03		7333360	19-Feb-08	APPARATUS FOR PULSE TESTING A MRAM DEVICE AND METHOD THEREFORE
GRANTED	SC12299ZP	USA	10/309514	03-Dec-02		6806127	19-Oct-04	METHOD AND STRUCTURE FOR CONTACTING AN OVERLYING ELECTRODE FOR A MAGNETOELECTRONICS ELEMENT
GRANTED	SC12299ZP	USA	10/922436	19-Aug-04		7042025	09-May-06	METHOD AND STRUCTURE FOR CONTACTING AN OVERLYING ELECTRODE FOR A MAGNETOELECTRONICS ELEMENT
GRANTED	SC12301ZP	USA	10/609288	27-Jun-03		6956763	18-Oct-05	MRAM ELEMENT AND METHODS FOR WRITING THE MRAM ELEMENT
GRANTED	SC12304ZP	USA	10/417537	16-Apr-03		6911156	28-Jun-05	METHODS FOR FABRICATING MRAM DEVICE STRUCTURES
GRANTED	SC12321TS	USA	10/302203	22-Nov-02		7082389	25-Jul-06	METHOD AND APPARATUS FOR SIMULATING A MAGNETORESISTIVE RANDOM ACCESS MEMORY (MRAM)
FILED	SC12420TC	CHIN	200480002158.7	16-Jan-04	13-Jul-05			MRAM ARCHITECTURE WITH A GROUNDED WRITE BIT LINE AND ELECTRICALLY ISOLATED READ BIT LINE
FILED	SC12420TC	JAPA	2006-500978	16-Jan-04	15-Jul-05			MRAM ARCHITECTURE WITH A GROUNDED WRITE BIT LINE AND ELECTRICALLY ISOLATED READ BIT LINE
FILED	SC12420TC	KORS	10-2005-7013046	16-Jan-04	14-Jul-05			MRAM ARCHITECTURE WITH A GROUNDED WRITE BIT LINE AND ELECTRICALLY ISOLATED READ BIT LINE
FILED	SC12420TC	TAIW	092135541	16-Dec-03				MRAM ARCHITECTURE WITH A GROUNDED

								WRITE BIT LINE AND ELECTRICALLY ISOLATED READ BIT LINE MRAM ARCHITECTURE WITH A GROUNDED WRITE BIT LINE AND ELECTRICALLY
GRANTED	SC12420TC	USA	10/346256	17-Jan-03		6714442	30-Mar-04	ISOLATED READ BIT LINE
GRANTED	SC12594ZP	USA	10/421095	22-Apr-03		6798004	28-Sep-04	MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICES AND METHODS FOR FABRICATING THE SAME
GRANTED	SC12594ZP	USA	10/912979	05-Aug-04		7169622	30-Jan-07	MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICES AND METHODS FOR FABRICATING THE SAME
FILED	SC12595ZP	CHIN	200480010848.7	16-Apr-04	21-Oct-05			METHODS FOR CONTACTING CONDUCTING LAYERS OVERLYING MAGENTOELECTRONIC ELEMENTS OF MRAM DEVICES
FILED	SC12595ZP	JAPA	2006-513086	16-Apr-04	24-Oct-05			METHODS FOR CONTACTING CONDUCTING LAYERS OVERLYING MAGENTOELECTRONIC ELEMENTS OF MRAM DEVICES
FILED	SC12595ZP	KORS	10-2005-7020063	16-Apr-04	21-Oct-05			METHODS FOR CONTACTING CONDUCTING LAYERS OVERLYING MAGENTOELECTRONIC ELEMENTS OF MRAM DEVICES
FILED	SC12595ZP	TAIW	093111295	22-Apr-04				METHODS FOR CONTACTING CONDUCTING LAYERS OVERLYING MAGENTOELECTRONIC ELEMENTS OF MRAM DEVICES
GRANTED	SC12595ZP	USA	10/421096	22-Apr-03		6881351	19-Apr-05	METHODS FOR CONTACTING CONDUCTING LAYERS OVERLYING MAGENTOELECTRONIC ELEMENTS OF MRAM DEVICES
FILED	SC12595ZP	USA	11/050191	02-Feb-05				METHODS FOR CONTACTING CONDUCTING LAYERS OVERLYING MAGNETOELECTRONIC ELEMENTS OF MRAM DEVICES
FILED	SC12596ZP	CHIN	200480010000.4	16-Apr-04				MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC12596ZP	JAPA	2006-513082	16-Apr-04	17-Oct-05			MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC12596ZP	KORS	10-2005-7019569	16-Apr-04	14-Oct-05			MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC12596ZP	TAIW	093110733	16-Apr-04				MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND METHODS FOR FABRICATING THE SAME
GRANTED	SC12596ZP	USA	10/417851	16-Apr-03		6784510	31-Aug-04	MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND METHODS FOR FABRICATING THE SAME
GRANTED	SC12596ZP	USA	10/885869	06-Jul-04		6890770	10-May-05	MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND

								METHODS FOR FABRICATING THE SAME
FILED	SC12636TC	CHIN	200480025448.3	15-Jul-04				WRITE DRIVER FOR A MAGNETO-RESISTIVE MEMORY
FILED	SC12636TC	JAPA	2006-525321	15-Jul-04	22-Feb-06			WRITE DRIVER FOR A MAGNETO-RESISTIVE MEMORY
FILED	SC12636TC	KORS	10-2006-7004467	15-Jul-04	03-Mar-06			WRITE DRIVER FOR A MAGNETO-RESISTIVE MEMORY
FILED	SC12636TC	TAIW	093124252	12-Aug-04				WRITE DRIVER FOR A MAGNETO-RESISTIVE MEMORY
GRANTED	SC12636TC	USA	10/656676	05-Sep-03		6842365	11-Jan-05	WRITE DRIVER FOR A MAGNETO-RESISTIVE MEMORY
GRANTED	SC12662TC	USA	10/401195	27-Mar-03		6667899	23-Dec-03	MAGNETIC MEMORY AND METHOD OF BI-DIRECTIONAL WRITE CURRENT PROGRAMMING
GRANTED	SC12691ZC	USA	10/737114	16-Dec-03		7088608	08-Aug-06	REDUCING POWER CONSUMPTION DURING MRAM WRITES USING MULTIPLE CURRENT LEVELS
GRANTED	SC12894TC	USA	10/656646	05-Sep-03		6859388	22-Feb-05	CIRCUIT FOR WRITE FIELD DISTURBANCE CANCELLATION IN AN MRAM AND METHOD OF OPERATION
FILED	SC12908ZP	CHIN	200480036273.6	29-Oct-04	06-Jun-06			MRAM DEVICE INTEGRATED WITH OTHER TYPES OF CIRCUITRY
FILED	SC12908ZP	JAPA	2006-543814	29-Oct-04	08-Jun-06			MRAM DEVICE INTEGRATED WITH OTHER TYPES OF CIRCUITRY
FILED	SC12908ZP	KORS	10-2006-7011250	29-Oct-04	08-Jun-06			MRAM DEVICE INTEGRATED WITH OTHER TYPES OF CIRCUITRY
FILED	SC12908ZP	TAIW	093137531	03-Dec-04				MRAM DEVICE INTEGRATED WITH OTHER TYPES OF CIRCUITRY
GRANTED	SC12908ZP	USA	10/730239	08-Dec-03		7031183	18-Apr-06	MRAM DEVICE INTEGRATED WITH OTHER TYPES OF CIRCUITRY
FILED	SC13021ZP	CHIN	200480030104.1	20-Oct-04	13-Apr-06			COMPOSITIONS AND METHODS FOR THE ELECTROLESS DEPOSITION OF NIFE ON A WORK PIECE
FILED	SC13021ZP	JAPA	2006-538102	20-Oct-04	13-Apr-06			COMPOSITIONS AND METHODS FOR THE ELECTROLESS DEPOSITION OF NIFE ON A WORK PIECE
FILED	SC13021ZP	KORS	10-2006-7008806	20-Oct-04	04-May-06			COMPOSITIONS AND METHODS FOR THE ELECTROLESS DEPOSITION OF NIFE ON A WORK PIECE
FILED	SC13021ZP	TAIW	093133236	01-Nov-04				COMPOSITIONS AND METHODS FOR THE ELECTROLESS DEPOSITION OF NIFE ON A WORK PIECE
FILED	SC13021ZP	USA	10/702909	05-Nov-03				COMPOSITIONS AND METHODS FOR THE ELECTROLESS DEPOSITION OF NIFE ON A WORK PIECE

FILED	SC13035ZP	CHIN	200480037446.6	04-Nov-04	15-Jun-06			SYNTHETIC ANTIFERROMAGNET STRUCTURES FOR USE IN MTJS IN MRAM TECHNOLOGY
FILED	SC13035ZP	EPC	04810475.6	04-Nov-04	29-May-06			SYNTHETIC ANTIFERROMAGNET STRUCTURES FOR USE IN MTJS IN MRAM TECHNOLOGY
FILED	SC13035ZP	JAPA	2006-545636	04-Nov-04	22-May-06			SYNTHETIC ANTIFERROMAGNET STRUCTURES FOR USE IN MTJS IN MRAM TECHNOLOGY
FILED	SC13035ZP	KORS	10-2006-7011933	04-Nov-04	16-Jun-06			SYNTHETIC ANTIFERROMAGNET STRUCTURES FOR USE IN MTJS IN MRAM TECHNOLOGY
FILED	SC13035ZP	TAIW	093138819	14-Dec-04				SYNTHETIC ANTIFERROMAGNET STRUCTURES FOR USE IN MTJS IN MRAM TECHNOLOGY
GRANTED	SC13035ZP	USA	10/740338	18-Dec-03		6946697	20-Sep-05	SYNTHETIC ANTIFERROMAGNET STRUCTURES FOR USE IN MTJS IN MRAM TECHNOLOGY
GRANTED	SC13035ZP	USA	11/182149	15-Jul-05		7226796	05-Jun-07	SYNTHETIC ANTIFERROMAGNET STRUCTURES FOR USE IN MTJS IN MRAM TECHNOLOGY
GRANTED	SC13069ZP	USA	11/048015	31-Jan-05		7087972	08-Aug-06	MAGNETOELECTRONIC DEVICES UTILIZING PROTECTIVE CAPPING LAYERS AND METHODS OF FABRICATING THE SAME
FILED	SC13093ZP	CHIN	200580036418.7	25-Oct-05	24-Apr-07			METHODS AND STRUCTURES FOR ELECTRICAL COMMUNICATION WITH AN OVERLYING ELECTRODE FOR A SEMICONDUCTOR ELEMENT
FILED	SC13093ZP	EPC	05812582.4	25-Oct-05				METHODS AND STRUCTURES FOR ELECTRICAL COMMUNICATION WITH AN OVERLYING ELECTRODE FOR A SEMICONDUCTOR ELEMENT
FILED	SC13093ZP	KORS	10-2007-7011249	25-Oct-05	17-May-07			METHODS AND STRUCTURES FOR ELECTRICAL COMMUNICATION WITH AN OVERLYING ELECTRODE FOR A SEMICONDUCTOR ELEMENT
FILED	SC13093ZP	TAIW	094139491	10-Nov-05				METHODS AND STRUCTURES FOR ELECTRICAL COMMUNICATION WITH AN OVERLYING ELECTRODE FOR A SEMICONDUCTOR ELEMENT
GRANTED	SC13093ZP	USA	10/993196	18-Nov-04		7105903	12-Sep-06	METHODS AND STRUCTURES FOR ELECTRICAL COMMUNICATION WITH AN OVERLYING ELECTRODE FOR A SEMICONDUCTOR ELEMENT
GRANTED	SC13123TC	USA	10/736852	16-Dec-03		7370260	06-May-08	MRAM HAVING ERROR CORRECTION CODE CIRCUITRY AND METHOD THEREFOR

GRANTED	SC13159TC	USA	10/806612	23-Mar-04		7266486	04-Sep-07	MAGNETORESISTIVE RANDOM ACCESS MEMORY SIMULATION
GRANTED	SC13230TC	USA	10/924631	24-Aug-04		7012841	14-Mar-06	CIRCUIT AND METHOD FOR CURRENT PULSE CONPENSATION
FILED	SC13340ZP	CHIN	200580036722.1	21-Nov-05	25-Apr-07			REDUCED POWER MAGNETORESISTIVE RANDOM ACCESS MEMORY ELEMENTS
FILED	SC13340ZP	JAPA	2007-543529	21-Nov-05	16-May-07			REDUCED POWER MAGNETORESISTIVE RANDOM ACCESS MEMORY ELEMENTS
FILED	SC13340ZP	KORS	10-2007-7011707	21-Nov-05	23-May-07			REDUCED POWER MAGNETORESISTIVE RANDOM ACCESS MEMORY ELEMENTS
FILED	SC13340ZP	PCT	PCT/US05/42764	21-Nov-05				REDUCED POWER MAGNETORESISTIVE RANDOM ACCESS MEMORY ELEMENTS
FILED	SC13340ZP	TAIW	094141302	24-Nov-05	24-Nov-05			REDUCED POWER MAGNETORESISTIVE RANDOM ACCESS MEMORY ELEMENTS
GRANTED	SC13340ZP	USA	10/997118	24-Nov-04		7129098	31-Oct-06	REDUCED POWER MAGNETORESISTIVE RANDOM ACCESS MEMORY ELEMENTS
GRANTED	SC13340ZP	USA	11/581951	16-Oct-06		7329935	12-Feb-08	REDUCED POWER MAGNETORESISTIVE RANDOM ACCESS MEMORY ELEMENTS
FILED	SC13341ZP	CHIN	200580034110.9	27-Sep-05	06-Apr-07			SPIN-TRANSFER BASED MRAM USING ANGULAR-DEPENDENT SELECTIVITY
FILED	SC13341ZP	EPC	05798779.4	27-Sep-05	10-Apr-07			SPIN-TRANSFER BASED MRAM USING ANGULAR-DEPENDENT SELECTIVITY
FILED	SC13341ZP	JAPA	2007-537901	27-Sep-05	28-Mar-07			SPIN-TRANSFER BASED MRAM USING ANGULAR-DEPENDENT SELECTIVITY
FILED	SC13341ZP	PCT	PCT/US05/34260	27-Sep-05				SPIN-TRANSFER BASED MRAM USING ANGULAR-DEPENDENT SELECTIVITY
GRANTED	SC13341ZP	USA	10/971741	22-Oct-04		7149106	12-Dec-06	SPIN-TRANSFER BASED MRAM USING ANGULAR-DEPENDENT SELECTIVITY
FILED	SC13343ZP	CHIN	200580023937.X	16-Jun-05	16-Jan-07			MAGNETIC TUNNEL JUNCTION ELEMENT STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC13343ZP	INDI	7277/DELNP/2006	16-Jun-05	01-Dec-06			MAGNETIC TUNNEL JUNCTION ELEMENT STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC13343ZP	JAPA	2007-523558	16-Jun-05	25-Dec-06			MAGNETIC TUNNEL JUNCTION ELEMENT STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC13343ZP	KORS	10-2007-7002017	16-Jun-05	26-Jan-07			MAGNETIC TUNNEL JUNCTION ELEMENT STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC13343ZP	PCT	PCT/US05/21311	16-Jun-05				MAGNETIC TUNNEL JUNCTION ELEMENT STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC13343ZP	TAIW	094123606	12-Jul-05				MAGNETIC TUNNEL JUNCTION ELEMENT STRUCTURES AND METHODS FOR

								FABRICATING THE SAME
GRANTED	SC13343ZP	USA	10/899610	26-Jul-04		7098495	29-Aug-06	MAGNETIC TUNNEL JUNCTION ELEMENT STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC13434TC	JAPA	2008-512281	07-Apr-06	08-Nov-07			NONVOLATILE MEMORY SYSTEM USING MAGNETO-RESISTIVE RANDOM ACCESS MEMORY (MRAM)
FILED	SC13434TC	KORS	10-2007-7026755	07-Apr-06	16-Nov-07			NONVOLATILE MEMORY SYSTEM USING MAGNETO-RESISTIVE RANDOM ACCESS MEMORY (MRAM)
GRANTED	SC13434TC	USA	11/130351	16-May-05		7245527	17-Jul-07	NONVOLATILE MEMORY SYSTEM USING MAGNETO-RESISTIVE RANDOM ACCESS MEMORY (MRAM)
GRANTED	SC13481ZP	USA	11/066884	24-Feb-05		7285835	23-Oct-07	LOW POWER MAGNETOELECTONIC DEVICE STRUCTURES UTILIZING ENHANCED PERMEABILITY MATERIALS
FILED	SC13481ZP	USA	11/867189	04-Oct-07				LOW POWER MAGNETOELECTRONIC DEVICE STRUCTURES UTILIZING ENHANCED PERMEABILITY MATERIALS
FILED	SC13491ZC	JAPA	2008-508840	02-Mar-06	24-Oct-07			TRIPLE PULSE METHOD FOR MRAM TOGGLE BIT CHARACTERIZATION
FILED	SC13491ZC	KORS	10-2007-7024961	02-Mar-06	29-Oct-07			TRIPLE PULSE METHOD FOR MRAM TOGGLE BIT CHARACTERIZATION
GRANTED	SC13491ZC	USA	11/118145	29-Apr-05		7158407	02-Jan-07	TRIPLE PULSE METHOD FOR MRAM TOGGLE BIT CHARACTERIZATION
FILED	SC13532ZP	CHIN	200580036437.X	30-Sep-05	24-Apr-07			MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC13532ZP	EPC	05812279.7	30-Sep-05				MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC13532ZP	INDI	1577/DELNP/2007	30-Sep-05	27-Feb-07			MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC13532ZP	JAPA	2007-538941	30-Sep-05	26-Apr-07			MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC13532ZP	KORS	10-2007-7011879	30-Sep-05	25-May-07			MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND METHODS FOR FABRICATING THE SAME
FILED	SC13532ZP	TAIW	094137203	24-Oct-05				MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND METHODS FOR FABRICATING THE SAME
GRANTED	SC13532ZP	USA	10/977003	27-Oct-04		7144744	05-Dec-06	MAGNETORESISTIVE RANDOM ACCESS MEMORY DEVICE STRUCTURES AND

								METHODS FOR FABRICATING THE SAME
FILED	SC13653TC	TAIW	094147046	28-Dec-05				TOGGLE MEMORY BURST
FILED	SC13653TC	USA	11/047544	31-Jan-05				TOGGLE MEMORY BURST
FILED	SC13879TC	TAIW	095141535	09-Nov-06				MRAM WITH A WRITE DRIVER AND METHOD THEREFOR
GRANTED	SC13879TC	USA	11/297202	07-Dec-05		7280388	09-Oct-07	MRAM WITH A WRITE DRIVER AND METHOD THEREFOR
FILED	SC13879TC	USA	11/848070	30-Aug-07				MRAM WITH A WRITE DRIVER AND METHOD THEREFOR
FILED	SC13955TC	CHIN	200680020367.3	13-Jun-06	07-Dec-07			ANTIFUSE CIRCUIT
FILED	SC13955TC	EPC	06784865.5	13-Jun-06	12-Dec-07			ANTIFUSE CIRCUIT
FILED	SC13955TC	JAPA	2008-518239	13-Jun-06	28-Nov-07			ANTIFUSE CIRCUIT
FILED	SC13955TC	KORS	10-2007-7030153	13-Jun-06	24-Dec-07			ANTIFUSE CIRCUIT
FILED	SC13955TC	TAIW	095121134	14-Jun-06				ANTIFUSE CIRCUIT
GRANTED	SC13955TC	USA	11/166139	24-Jun-05		7224630	29-May-07	ANTIFUSE CIRCUIT
FILED	SC13955TC	USA	11/737506	19-Apr-07				ANTIFUSE CIRCUIT
GRANTED	SC13976TC	USA	11/297203	07-Dec-05		7206223	17-Apr-07	MRAM MEMORY WITH RESIDUAL WRITE FIELD RESET
FILED	SC14010ZP	CHIN	200680027836.4	24-Jul-06	29-Jan-08			METHOD FOR TUNNEL JUNCTION SENSOR WITH MAGNETIC CLADDING
FILED	SC14010ZP	KORS	10-2008-7002342	24-Jul-06	29-Jan-08			METHOD FOR TUNNEL JUNCTION SENSOR WITH MAGNETIC CLADDING
FILED	SC14010ZP	TAIW	095127611	28-Jul-06				METHOD FOR TUNNEL JUNCTION SENSOR WITH MAGNETIC CLADDING
FILED	SC14010ZP	USA	11/192517	29-Jul-05				METHOD FOR TUNNEL JUNCTION SENSOR WITH MAGNETIC CLADDING
FILED	SC14011ZP	JAPA	PCT/US06/28576	24-Jul-06	29-Jan-08			MAGNETIC TUNNEL JUNCTION SENSOR
FILED	SC14011ZP	KORS	10-2008-7002294	24-Jul-06	28-Jan-08			MAGNETIC TUNNEL JUNCTION SENSOR
FILED	SC14011ZP	TAIW	095127621	28-Jul-06				MAGNETIC TUNNEL JUNCTION SENSOR
FILED	SC14011ZP	USA	11/192569	29-Jul-05				MAGNETIC TUNNEL JUNCTION SENSOR
FILED	SC14012ZP	JAPA	PCT/US2006/030817	08-Aug-06	26-Feb-08			PASSIVE ELEMENTS IN MRAM EMBEDDED INTEGRATED CIRCUITS
FILED	SC14012ZP	KORS	10-2008-7004934	08-Aug-06	28-Feb-08			PASSIVE ELEMENTS IN MRAM EMBEDDED INTEGRATED CIRCUITS
FILED	SC14012ZP	TAIW	095130197	17-Aug-06				PASSIVE ELEMENTS IN MRAM EMBEDDED INTEGRATED CIRCUITS
GRANTED	SC14012ZP	USA	11/217146	31-Aug-05		7264985	04-Sep-07	PASSIVE ELEMENTS IN MRAM EMBEDDED INTEGRATED CIRCUITS
FILED	SC14013ZP	CHIN	200680022985.1	22-Jun-06	26-Dec-07			MRAM EMBEDDED SMART POWER INTEGRATED CIRCUITS
FILED	SC14013ZP	JAPA	2008-520255	22-Jun-06	04-Jan-08			MRAM EMBEDDED SMART POWER INTEGRATED CIRCUITS

FILED	SC14013ZP	TAIW	095122403	22-Jun-06				MRAM EMBEDDED SMART POWER INTEGRATED CIRCUITS
GRANTED	SC14013ZP	USA	11/170874	30-Jun-05		7324369	29-Jan-08	MRAM EMBEDDED SMART POWER INTEGRATED CIRCUITS
FILED	SC14014ZP	JAPA	PCT/US2006/041147	20-Oct-06	28-Apr-08			MAGNETIC TUNNEL JUNCTION CURRENT SENSORS
FILED	SC14014ZP	KORS	10-2008-7010161	20-Oct-06	28-Apr-08			MAGNETIC TUNNEL JUNCTION CURRENT SENSORS
FILED	SC14014ZP	TAIW	095139650	27-Oct-06				MAGNETIC TUNNEL JUNCTION CURRENT SENSORS
GRANTED	SC14014ZP	USA	11/262053	28-Oct-05		7239543	03-Jul-07	MAGNETIC TUNNEL JUNCTION CURRENT SENSORS
FILED	SC14015ZP	CHIN	200680017817.3	09-May-06	22-Nov-07			3-D INDUCTOR AND TRANSFORMER DEVICES IN MRAM EMBEDDED INTEGRATED CIRCUITS
FILED	SC14015ZP	JAPA	2008-515709	09-May-06	31-Oct-07			3-D INDUCTOR AND TRANSFORMER DEVICES IN MRAM EMBEDDED INTEGRATED CIRCUITS
FILED	SC14015ZP	TAIW	095117297	16-May-06				3-D INDUCTOR AND TRANSFORMER DEVICES IN MRAM EMBEDDED INTEGRATED CIRCUITS
GRANTED	SC14015ZP	USA	11/147599	07-Jun-05		7262069	28-Aug-07	3-D INDUCTOR AND TRANSFORMER DEVICES IN MRAM EMBEDDED INTEGRATED CIRCUITS
FILED	SC14016ZP	CHIN	PCT/US2006/060208	25-Oct-06	28-Apr-08			MAGNETIC TUNNEL JUNCTION PRESSURE SENSORS AND METHODS
FILED	SC14016ZP	SING	200802833-4	25-Oct-06	11-Apr-08			MAGNETIC TUNNEL JUNCTION PRESSURE SENSORS AND METHODS
FILED	SC14016ZP	TAIW	095139674	27-Oct-06				MAGNETIC TUNNEL JUNCTION PRESSURE SENSORS AND METHODS
FILED	SC14016ZP	USA	11/262064	28-Oct-05				MAGNETIC TUNNEL JUNCTION PRESSURE SENSORS AND METHODS
FILED	SC14017ZP	CHIN	200680036269.9	20-Sep-06	28-Mar-08			MAGNETIC TUNNEL JUNCTION TEMPERATURE SENSORS
FILED	SC14017ZP	KORS	10-2008-7007630	20-Sep-06	28-Mar-08			MAGNETIC TUNNEL JUNCTION TEMPERATURE SENSORS
FILED	SC14017ZP	TAIW	095135056	22-Sep-06				MAGNETIC TUNNEL JUNCTION TEMPERATURE SENSORS
FILED	SC14017ZP	USA	11/240514	30-Sep-05				MAGNETIC TUNNEL JUNCTION TEMPERATURE SENSORS
FILED	SC14052ZP	CHIN	PCT/US2006/041148	20-Oct-06	28-Apr-08			METHODS OF IMPLEMENTING MAGNETIC TUNNEL JUNCTION CURRENT SENSORS
FILED	SC14052ZP	SING	200802820-1	20-Oct-06	11-Apr-08			METHODS OF IMPLEMENTING MAGNETIC TUNNEL JUNCTION CURRENT SENSORS
FILED	SC14052ZP	TAIW	095139683	27-Oct-06				METHODS OF IMPLEMENTING MAGNETIC TUNNEL JUNCTION CURRENT SENSORS
GRANTED	SC14052ZP	USA	11/262054	28-Oct-05		7271011	18-Sep-07	METHODS OF IMPLEMENTING MAGNETIC TUNNEL JUNCTION CURRENT SENSORS
FILED	SC14058ZP	CHIN	200680027876.9	28-Jun-06	29-Jan-08			MAGNETIC TUNNEL JUNCTION SENSOR

								METHOD
FILED	SC14058ZP	KORS	10-2008-7002350	28-Jun-06	29-Jan-08			MAGNETIC TUNNEL JUNCTION SENSOR METHOD
FILED	SC14058ZP	TAIW	095126316	19-Jul-06				MAGNETIC TUNNEL JUNCTION SENSOR METHOD
GRANTED	SC14058ZP	USA	11/192570	29-Jul-05		7220602	22-May-07	MAGNETIC TUNNEL JUNCTION SENSOR METHOD
FILED	SC14082ZP	CHIN	PCT/US2006/036634	20-Sep-06	31-Mar-08			MAGNETIC TUNNEL JUNCTION TEMPERATURE SENSORS AND METHODS
FILED	SC14082ZP	SING	200801723-8	20-Sep-06	29-Feb-08			MAGNETIC TUNNEL JUNCTION TEMPERATURE SENSORS AND METHODS
FILED	SC14082ZP	TAIW	095135055	22-Sep-06				MAGNETIC TUNNEL JUNCTION TEMPERATURE SENSORS AND METHODS
FILED	SC14082ZP	USA	11/239884	30-Sep-05				MAGNETIC TUNNEL JUNCTION TEMPERATURE SENSORS AND METHODS
FILED	SC14085ZP	JAPA	PCT/US06/28574	24-Jul-06	29-Jan-08			TUNNEL JUNCTION SENSOR WITH MAGNETIC CLADDING
FILED	SC14085ZP	KORS	10-2008-7002363	24-Jul-06	29-Jan-08			TUNNEL JUNCTION SENSOR WITH MAGNETIC CLADDING
FILED	SC14085ZP	TAIW	095127622	28-Jul-06				TUNNEL JUNCTION SENSOR WITH MAGNETIC CLADDING
FILED	SC14085ZP	USA	11/192802	29-Jul-05				TUNNEL JUNCTION SENSOR WITH MAGNETIC CLADDING
FILED	SC14623ZP	USA	11/416850	02-May-06				METHODS AND APPARATUS FOR A MEMORY DEVICE WITH SELF-HEALING REFERENCE BITS
FILED	SC14624ZP	TAIW	095149376	28-Dec-06				MAGNETIC TUNNEL JUNCTION DEVICE WITH IMPROVED BARRIER LAYER
FILED	SC14624ZP	USA	11/341986	27-Jan-06				MAGNETIC TUNNEL JUNCTION DEVICE WITH IMPROVED BARRIER LAYER
FILED	SC14653ZP	USA	11/225973	13-Sep-05				OSCILLATOR AND METHOD OF MANUFACTURE
FILED	SC14679ZP	PCT	PCT/US2007/063045	01-Mar-07				METHODS AND APPARATUS FOR A SYNTHETIC ANTI-FERROMAGNET STRUCTURE WITH REDUCED TEMPERATURE DEPENDENCE
FILED	SC14679ZP	TAIW	096109374	19-Mar-07				METHODS AND APPARATUS FOR A SYNTHETIC ANTI-FERROMAGNET STRUCTURE WITH REDUCED TEMPERATURE DEPENDENCE
FILED	SC14679ZP	USA	11/406566	18-Apr-06				METHODS AND APPARATUS FOR A SYNTHETIC ANTI-FERROMAGNET STRUCTURE WITH REDUCED TEMPERATURE DEPENDENCE
FILED	SC14788ZP	USA	11/351610	10-Feb-06				METHOD OF MANUFACTURING A

								MAGNETOELECTRONIC DEVICE
GRANTED	SC91225A	USA	09/406415	27-Sep-99		6191973	20-Feb-01	MRAM CAM
GRANTED	SC91225A	USA	09/597362	19-Jun-00		6269016	31-Jul-01	MRAM CAM